

LMK6x 低抖动高性能 BAW 振荡器

1 特性

- 高性能差分 and 单端输出振荡器、支持以下范围内的任何固定频率：
 - LMK6D：1MHz 至 400MHz，LVDS 输出
 - LMK6H：1MHz 至 400MHz，HCSL 输出
 - LMK6P：1MHz 至 400MHz，LVPECL 输出
 - LMK6C：1MHz 至 200MHz，LVCMOS 输出
- 超低抖动：
 - LMK6D/LMK6H/LMK6P：频率为 156.25MHz 时 RMS 抖动典型值为 100fs，最大值为 125fs (12kHz 至 20MHz)
 - LMK6C：频率为 100MHz 时 RMS 抖动典型值为 350fs，最大值为 500fs (12kHz 至 20MHz)
 - LMK6H：符合 PCIe 第 1 代到第 6 代标准
- ± 25 ppm 的总频率稳定性 (考虑 10 年老化和其他因素)
- 超小型业界通用 DLE 和 DLF 封装
- 支持扩展工业温度等级：
 - LMK6P/LMK6D/LMK6H：-40°C 至 85°C
 - LMK6C：-40°C 至 105°C
- 集成 LDO，具有强大的抗电源噪声能力：
 - 在 500kHz 纹波下具有 -72dBc PSRR
- 启动时间：< 5ms
- 标准频率：
 - LVCMOS (MHz)：1、2.04、4、8.192、10、12、12.288、16、19.2、20、23.5、24、24.57、25、25.6、26、26.21、27、28.12、32.768、33.333、40、48、49.15、50、54、60、65.53、66、74.25、76.8、80、100、108、125、133.330 和 156.25
 - 差分 (MHz)：25、26、32.5、50、51.84、54、65、76.8、80、100、108、122.88、125、133.330、148.35、148.5、150、155.52、156.25、161.1328125、200、312.5 和 400
- 器件可支持 1MHz 至 400MHz 之间的任何频率。如有任何频率和样片需求，请与 TI 代表联系

2 应用

- 56G/112G PAM4 时钟
- 100G/200G/400G/800G 光纤传输网络和相干光学元件
- 网络设备、交换机、路由器、线路卡、SAN、数据中心和基带单元 (BBU)
- 符合 PCIe 第 1 代到第 6 代标准的参考时钟
- 工业应用
- 测试和测量

- ASIC、FPGA、MCU 参考时钟
- 高性能晶体振荡器替代产品

3 说明

德州仪器 (TI) 的体声波 (BAW) 是一种微谐振器技术，能够将高精度 BAW 谐振器直接集成到具有超低抖动时钟电路的封装中。与其他硅基制造工艺一样，BAW 完全由 TI 工厂设计和制造。

LMK6x 器件是一款超低抖动固定频率振荡器，融合了 BAW 作为谐振器源。该器件根据特定运行模式进行出厂编程，包括频率、电压、输出类型和功能引脚。LMK6x 带有高性能分数分频器，能够产生指定范围内的任何频率，提供可满足所有频率需求的单个器件系列。

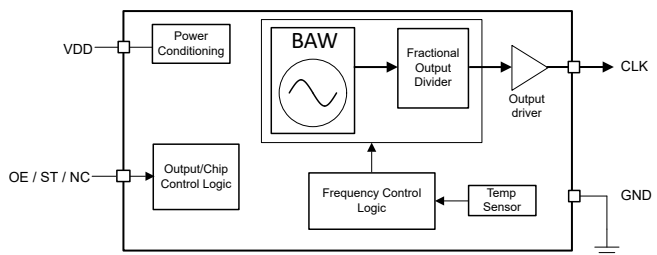
凭借高性能时钟、机械稳定性、灵活性和小型封装选项，此器件非常适用于电信、数据以及企业网络和工业应用中使用的高速 SERDES 内的参考时钟和核心时钟。

封装信息

器件型号	输出类型	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
LMK6C	LVCMOS	VSON (DLE-4)	3.2mm x 2.5mm
LMK6C		VSON (DLF-4)	2.5mm x 2mm
LMK6D LMK6H LMK6P	LVDS、HCSL、LVPECL	VSON (DLE-6)	3.2mm x 2.5mm
LMK6D LMK6H LMK6P		VSON (DLF-6)	2.5mm x 2mm

(1) 有关所有可选封装，请参阅 节 12。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。



LMK6x 简化方框图



Table of Contents

1 特性	1	8.2 Functional Block Diagram.....	22
2 应用	1	8.3 Feature Description.....	22
3 说明	1	8.4 Device Functional Modes.....	28
4 Device Ordering Information	3	9 Application and Implementation	29
5 Pin Configuration and Functions	5	9.1 Application Information.....	29
6 Specifications	6	9.2 Typical Application.....	29
6.1 Absolute Maximum Ratings.....	6	9.3 Power Supply Recommendations.....	32
6.2 ESD Ratings.....	6	9.4 Layout.....	32
6.3 Environmental Compliance.....	6	10 Device and Documentation Support	36
6.4 Recommended Operating Conditions.....	6	10.1 Documentation Support.....	36
6.5 Thermal Information.....	7	10.2 接收文档更新通知.....	36
6.6 Thermal Information.....	7	10.3 支持资源.....	36
6.7 Electrical Characteristics.....	8	10.4 Trademarks.....	36
6.8 Timing Diagrams.....	14	10.5 静电放电警告.....	36
6.9 Typical Characteristics.....	15	10.6 术语表.....	36
7 Parameter Measurement Information	20	11 Revision History	36
7.1 Device Output Configurations.....	20	12 Mechanical, Packaging, and Orderable Information	37
8 Detailed Description	22		
8.1 Overview.....	22		

4 Device Ordering Information

Use 图 4-1 and 图 4-2 to understand the device nomenclature of the LMK6x orderable options.

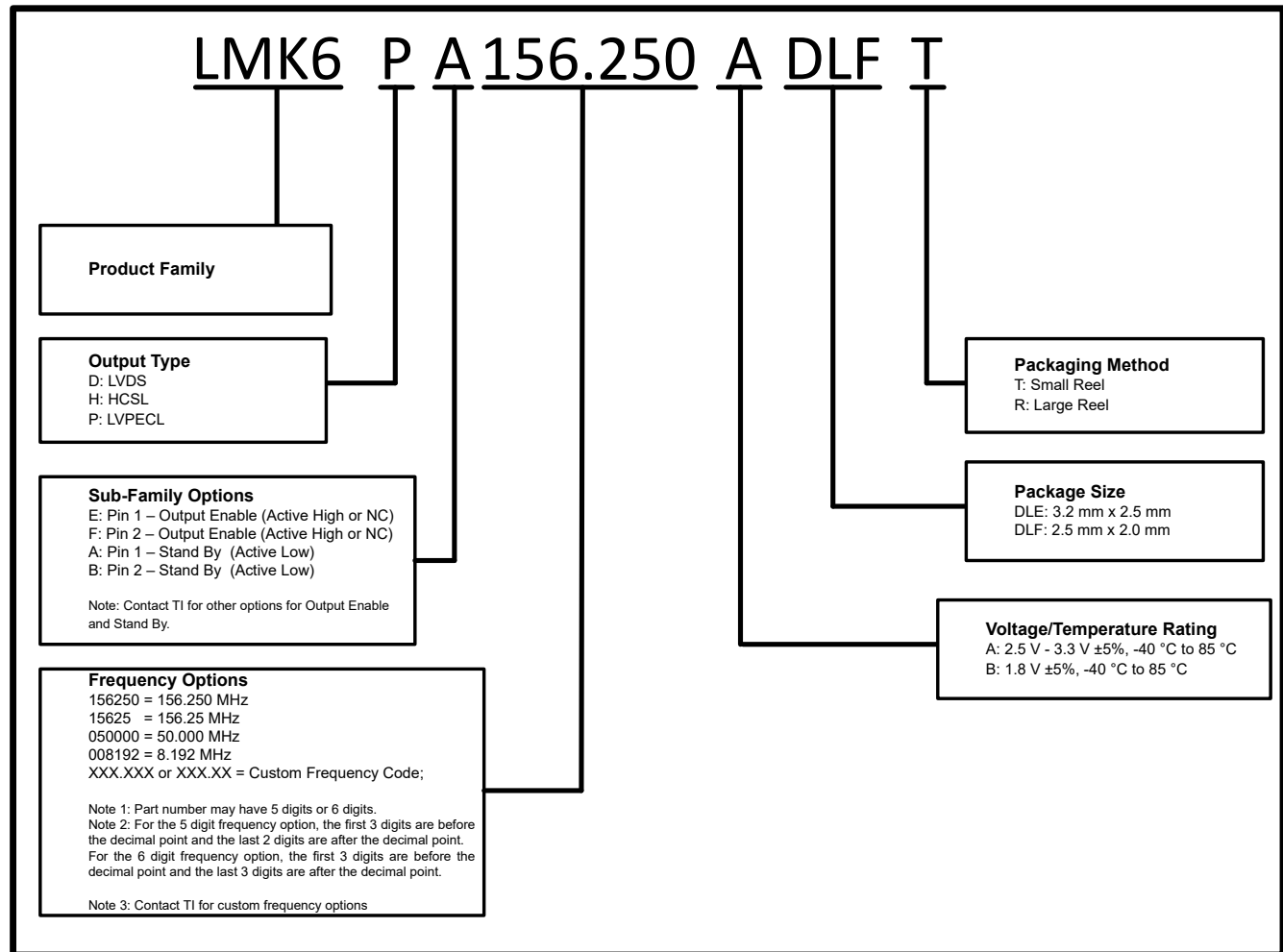


图 4-1. Part Number Guide: LMK6D, LMK6H, and LMK6P

Note: Contact a TI representative to pre-order specific devices. Email: ti_osc_customer_requirement@list.ti.com

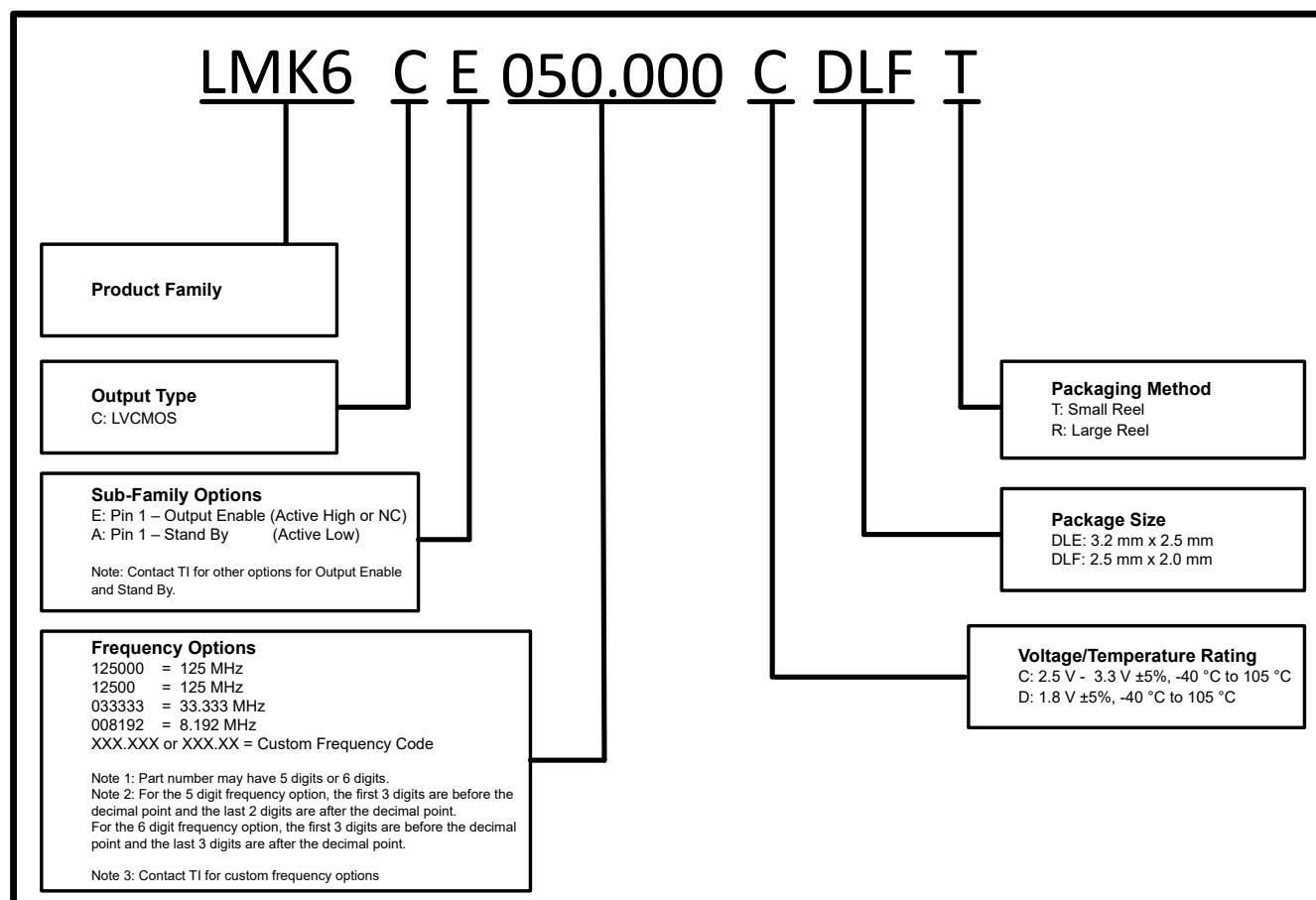


图 4-2. Part Number Guide: LMK6C

Note: Contact a TI representative to pre-order specific devices. Email: ti_osc_customer_requirement@list.ti.com

5 Pin Configuration and Functions

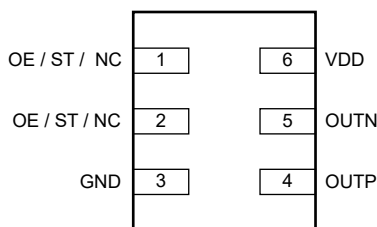


图 5-1. LMK6P, LMK6D, or LMK6H 6-Pin VSON (Top View)

表 5-1. LMK6P, LMK6D, or LMK6H Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	DLE/DLF		
OE / ST / NC	1	I / NC	Output Enable (OE) or Standby (ST) pin or No Connect (NC). See 表 8-1 for more details.
OE / ST / NC	2	NC / I	Output Enable (OE) or Standby (ST) pin or No Connect (NC). See 表 8-1 for more details.
GND	3	G	Device ground
OUTP	4	O	Positive differential output clock
OUTN	5	O	Negative differential output clock
VDD	6	P	Device power supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power, NC = No Connect (can be left floating).

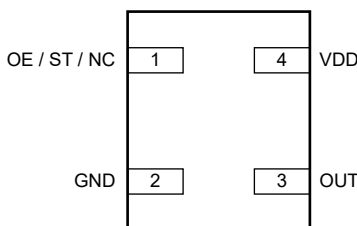


图 5-2. LMK6C 4-Pin VSON (Top View)

表 5-2. LMK6C Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	DLE/DLF		
OE / ST / NC	1	I / NC	Output Enable (OE) or Standby (ST) pin or No Connect (NC). See 表 8-2 for more details.
GND	2	G	Device ground
OUT	3	O	LVCMOS output clock
VDD	4	P	Device power supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power, NC = No Connect (can be left floating).

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
VDD	Device Supply Voltage ⁽²⁾	– 0.3	3.63	V
	Device Supply Voltage ⁽³⁾	– 0.3	1.98	V
EN	Logic Input Voltage	– 0.3	VDD + 0.3	V
OUTP, OUTN	Clock Output Voltage ⁽⁴⁾	– 0.3	VDD + 0.3	V
OUT	Clock Output Voltage ⁽⁵⁾	– 0.3	VDD + 0.3	V
T _J	Junction Temperature		125	°C
T _{STG}	Storage Temperature		150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) For all devices with Recommended Operating Voltage of 2.5 V +/- 5% and 3.3 V +/- 5%

(3) For all devices with Recommended Operating Voltage of 1.8 V +/- 5%

(4) For all differential outputs - LMK6D, LMK6H, and LMK6P.

(5) For single ended outputs - LMK6C.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC JS-002, all pins ⁽²⁾	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Environmental Compliance

		VALUE	UNIT
Mechanical Shock Resistance	MIL-STD-883F, Method 2002, Condition A	1500	g
Mechanical Vibration Resistance	MIL-STD-883F, Method 2026, Condition C	10	g
	MIL-STD-883F, Method 2007, Condition A	20	g
Moisture Sensitivity Level (MSL)		MSL1	

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDD	Device Supply Voltage ⁽¹⁾	1.7	1.8	1.9	V
	Device Supply Voltage ⁽²⁾	2.37	2.5, 3.3	3.5	V
T _A	Ambient temperature ⁽³⁾	– 40		85	°C
	Ambient temperature ⁽⁴⁾	– 40		105	°C
T _J	Junction temperature			125	°C
t _{RAMP}	VDD power-up ramp time ^{(1) (2)}	0.1		100	ms

(1) For all devices with Recommended Operating Voltage of 1.8V +/- 5%

(2) For all devices with Recommended Operating Voltage of 2.5V +/- 5% and 3.3V +/- 5%

(3) For all differential outputs - LMK6D, LMK6H and LMK6P.

(4) For single-ended output - LMK6C.

6.5 Thermal Information

THERMAL METRIC ⁽¹⁾		LMK6D/H/P		UNIT
		DLE (VSON)	DLF (VSON)	
		6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	101.2	107.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	58.6	70.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	31.3	39.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.7	2.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	31.1	39.2	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.6 Thermal Information

THERMAL METRIC ⁽¹⁾		LMK6C		UNIT
		DLE (VSON)	DLF (VSON)	
		4 PINS	4 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	124.8	128.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	61.2	73.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	42.5	39.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.8	2.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	42.3	39.5	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.7 Electrical Characteristics

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Current Consumption Characteristics						
I _{DD}	Device Power Consumption (LVPECL,VDD = 2.5 V/3.3 V, Excluding load current)	100 MHz		65	82	mA
		156.25 MHz		69	87	mA
		200 MHz		67	85	mA
		312.5 MHz		76	95	mA
		400 MHz		88	108	mA
	Device Power Consumption (LVPECL,VDD = 1.8 V, Excluding load current)	100 MHz		61	79	mA
		156.25 MHz		66	83	mA
		200 MHz		64	82	mA
		312.5 MHz		73	91	mA
		400 MHz		84	104	mA
	Device Power Consumption (HCSL,VDD = 2.5 V/3.3 V, Excluding load current)	100 MHz		65	82	mA
		156.25 MHz		69	87	mA
		200 MHz		67	86	mA
		312.5 MHz		76	96	mA
		400 MHz		88	108	mA
	Device Power Consumption (HCSL,VDD = 1.8 V, Excluding load current)	100 MHz		58	75	mA
		156.25 MHz		62	80	mA
		200 MHz		60	78	mA
		312.5 MHz		69	88	mA
		400 MHz		77	97	mA
	Device Power Consumption (LVDS,VDD = 2.5 V/3.3 V, Excluding load current)	100 MHz		54	71	mA
		156.25 MHz		58	75	mA
		200 MHz		56	74	mA
		312.5 MHz		65	84	mA
		400 MHz		76	96	mA
	Device Power Consumption (LVDS,VDD = 1.8 V, Excluding load current)	100 MHz		52	68	mA
		156.25 MHz		56	72	mA
		200 MHz		54	71	mA
		312.5 MHz		63	80	mA
		400 MHz		74	92	mA
	Device Power Consumption (LVCMOS,VDD = 2.5 V / 3.3 V, with load)	100 MHz		45	62	mA
		156.25 MHz		55	71	mA
		200 MHz		61	77	mA
	Device Power Consumption (LVCMOS,VDD = 1.8 V, with load)	100 MHz		44	59	mA
		156.25 MHz		50	65	mA
		200 MHz		56	72	mA
I _{DD-STBY}	Device Stand By current	ST (Stand By) = GND		6	13	mA
I _{DD-PD}	Device current with output disabled (100 MHz)	OE = GND, LVPECL mode, VDD = 3.3 V		48	67	mA
		OE = GND, HCSL mode, VDD = 3.3 V		49	67	mA
		OE = GND, LVDS mode, VDD = 3.3 V		49	66	mA
		OE = GND, LVCMOS mode, VDD = 3.3 V		40	56	mA
LVPECL Output Characteristics						

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS
Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
F _{out}	Output Frequency		1		400	MHz
V _{OD}	Output Voltage Swing (V _{OH} - V _{OL})	AC coupled, VDD = 3.3V	525	645	765	mV
		AC coupled, VDD = 2.5V	450	555	660	mV
		AC coupled, VDD = 1.8 V	280	375	470	mV
		DC coupled, VDD = 2.5 V/ 3.3 V ⁽¹⁾	650	800	950	mV
		DC coupled, VDD = 1.8 V ⁽¹⁾	450	600	750	mV
V _{OD,DIFF}	Differential Output peak-peak swing		2× V _{OD}			V _{pp}
V _{OS}	Output Common-Mode Voltage	VDD = 3.3 V ⁽¹⁾	1.5	1.6	1.7	V
		VDD = 2.5 V ⁽¹⁾	0.825	0.9	0.975	V
		VDD = 1.8 V ⁽¹⁾	0.45	0.5	0.55	V
t _R /t _F	Output Rise/Fall Time	20% to 80% of V _{OD,DIFF} , VDD = 2.5 V/ 3.3 V		120	200	ps
		20% to 80% of V _{OD,DIFF} , VDD = 1.8 V		120	200	ps
ODC	Output Duty Cycle	VDD = 2.5 V/ 3.3V, measured between 50% points on the waveform	45	50	55	%
		VDD = 1.8 V, measured between 50% points on the waveform	45	50	55	%
LVDS Output Characteristics						
F _{out}	Output Frequency		1		400	MHz
V _{OD}	Output Voltage Swing (V _{OH} - V _{OL})	Under LVDS Load condition	250	350	450	mV
V _{OD,DIFF}	Differential Output peak-peak swing		2× V _{OD}			V _{pp}
V _{OS}	Output Common Mode Voltage	VDD = 2.5V/3.3 V	1.025	1.2	1.375	V
		VDD = 1.8 V	0.80	0.9	1.0	V
t _R /t _F	Output Rise/Fall Time	20% to 80% of V _{OD,DIFF} , VDD = 2.5V/3.3 V		150	250	ps
		20% to 80% of V _{OD,DIFF} , VDD = 1.8V		150	250	ps
ODC	Output Duty Cycle	VDD = 2.5 V/3.3 V, measured between 50% points on the waveform	45	50	55	%
		VDD = 1.8V, measured between 50% points on the waveform	45	50	55	%
HCSL Output characteristics						
F _{out}	Output Frequency		1		400	MHz
V _{OH}	Output High Voltage	DC coupled, 50 ohms to ground, VDD = 2.5 V/ 3.3 V	650	750	850	mV
		DC coupled, 50 ohms to ground, VDD = 1.8 V	460	560	660	mV
V _{OL}	Output Low Voltage	DC coupled, 50 ohms to ground, VDD = 2.5 V/ 3.3 V	- 150	0	150	mV
		DC coupled, 50 ohms to ground, VDD = 1.8 V	- 150	0	150	mV
V _{OD,DIFF}	Differential Output peak-peak swing		2× V _{O H} - V _{OL}			V
V _{cross}	Absolute Crossing Point Voltage	VDD = 3.3 V / 2.5 V, f _{out} = 100 MHz	0.2	0.35	0.50	V _{pp}
		VDD = 1.8 V, f _{out} = 100 MHz	0.15	0.275	0.40	V _{pp}
V _{cross-delta}	Absolute Crossing Point Voltage variation	VDD = 3.3 V / 2.5 V / 1.8 V, f _{out} = 100 MHz		0.14		V

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
dV/dt	Output Slew Rate	50 ohms to ground; DC coupled load; measured slew rate in +/-150mV from Center.	2		12	V/ns
Δ dV/dt	Output Slew Rate variation				20	%
ODC	Output Duty Cycle		45	50	55	%
LVCMOS Output Characteristics						
F _{out}	Output Frequency		1		200	MHz
V _{OL}	Output Low Voltage	I _{OL} = 3.6 mA, VDD = 1.8 V			0.36	V
		I _{OL} = 5.0 mA, VDD = 2.5 V			0.5	V
		I _{OL} = 6.6 mA, VDD = 3.3 V			0.66	V
V _{OH}	Output High Voltage	I _{OH} = 3.6 mA, VDD = 1.8 V	1.44			V
		I _{OH} = 5.0 mA, VDD = 2.5 V	2			V
		I _{OH} = 6.6 mA, VDD = 3.3 V	2.64			V
t _R /t _F	Output Rise/Fall Time	20% to 80% of V _{OH} -V _{OL} , C _L = 2 pF		0.5	1	ns
ODC	Output Duty Cycle		45	50	55	%
R _{out}	Output Impedance	OE = HIGH	40	50	60	Ω
C _L	Maximum capacitive load	F _{out} > 50 MHz ⁽³⁾			15	pF
		F _{out} < 50 MHz ⁽³⁾			30	pF
Function Pin Input Characteristics (OE/ST pin)						
V _{IL}	Input Low Voltage				0.6	V
V _{IH}	Input High Voltage		1.3			V
I _{IL}	Input Low Current	OE = GND	-40			μA
I _{IH}	Input High Current	OE = VDD			40	μA
C _{IN}	Input Capacitance			2		pF
LVDS, HCSL and LVPECL Frequency Tolerance						
F _T	Total Frequency Stability	Inclusive of: solder shift, initial tolerance, variation over -40°C to 85°C, variation over rated supply voltage range, and 10 year aging at 25°C.	- 25		25	ppm
		Inclusive of: solder shift, initial tolerance, variation over -40°C to 85°C, variation over supply voltage range.	- 20		20	ppm
LVCMOS Frequency Tolerance						
F _T	Total Frequency Stability	Inclusive of: solder shift, initial tolerance, variation over -40°C to 105°C, variation over rated supply voltage range, and 10 year aging at 25°C.	-25		25	ppm
		Inclusive of: solder shift, initial tolerance, variation over -40°C to 105°C, variation over rated supply voltage range.	-20		20	ppm
Differential output PSRR Characteristics						
PSRR	Spur induced by 50 mV power supply ripple at 156.25 MHz output, VDD = 2.5 V/3.3 V, No power supply decoupling capacitor	Sine wave at 50 kHz		- 71		dBc
		Sine wave at 100 kHz		- 71		dBc
		Sine wave at 500 kHz		- 72		dBc
		Sine wave at 1 MHz		- 70		dBc

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
PSRR	Spur induced by 50 mV power supply ripple at 156.25 MHz output, VDD = 1.8 V, No power supply decoupling capacitor	Sine wave at 50 kHz		- 64		dBc
		Sine wave at 100 kHz		- 64		dBc
		Sine wave at 500 kHz		- 67		dBc
		Sine wave at 1 MHz		- 68		dBc
PSRR	Jitter sensitivity to Power supply ripple;	100 kHz sine wave ripple, 3.3 V Supply ⁽²⁾		4		fs/mV
LVCMOS PSRR Characteristics						
PSRR	Spur induced by 50 mV power supply ripple at 50MHz output, VDD = 2.5V/3.3 V, No power supply decoupling capacitor	Sine wave at 50 kHz		- 72		dBc
		Sine wave at 100 kHz		- 71		dBc
		Sine wave at 500 kHz		- 70		dBc
		Sine wave at 1 MHz		- 69		dBc
PSRR	Spur induced by 50 mV power supply ripple at 50MHz output, VDD = 1.8V, No power supply decoupling capacitor	Sine wave at 50 kHz		- 50		dBc
		Sine wave at 100 kHz		- 50		dBc
		Sine wave at 500 kHz		- 52		dBc
		Sine wave at 1 MHz		- 55		dBc
PSRR	Jitter sensitivity to Power supply ripple;	100 kHz sine wave ripple, 3.3 V Supply ⁽²⁾		10		fs/mV
Power-On Characteristics						
t _{START_UP}	Start-up Time	Time elapsed from 0.95 x VDD until output is enabled and output is within specification; Tested with a VDD supply ramp time of around 200 μ s			5	ms
t _{OE-EN}	Output Enable Time	Time elapsed from OE = V _{IH} until output is enabled and output is within specification, F _{out} > 10 MHz			25	μ s
t _{OE-DIS}	Output Disable Time	Time elapsed from OE = V _{IL} until output is disabled, F _{out} > 10 MHz			1	μ s
LVPECL - Clock Output Jitter						
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 156.25 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 156.25 MHz.		- 95		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 127		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 146		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 156		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 158		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 312.5 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 312.5 MHz.		- 89		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 121		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 140		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 150		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 154		dBc/Hz

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS
Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 100 MHz		125	170	fs
		F _{out} = 125 MHz		100	125	fs
		F _{out} = 155.52 MHz		100	125	fs
		F _{out} = 161.1328125 MHz		110	150	fs
		F _{out} = 200 MHz		120	150	fs
		F _{out} = 400 MHz		100	135	fs
R _{PeriodJITT} ,RMS	RMS Period Jitter	F _{out} ≥ 25 MHz		1.7		ps
R _{JITT} ,PK-PK	Peak-peak Period Jitter	F _{out} ≥ 25 MHz		13		ps
LVDS - Clock Output Jitter						
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 156.25 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 156.25 MHz		- 95		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 128		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 146		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 156		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 156.5		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 312.5 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 312.5 MHz.		- 89		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 122		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 139		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 150		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 153.5		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 100 MHz		140	170	fs
		F _{out} = 125 MHz		110	125	fs
		F _{out} = 155.52 MHz		105	140	fs
		F _{out} = 161.1328125 MHz		125	160	fs
		F _{out} = 200 MHz		125	150	fs
		F _{out} = 400 MHz		100	135	fs
R _{PeriodJITT} ,RMS	RMS Period Jitter	F _{out} ≥ 25 MHz		1.6		ps
R _{JITT} ,PK-PK	Peak-peak Period Jitter	F _{out} ≥ 25 MHz		13		ps
HCSL - Clock output jitter						

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
J _{PCle1-cc}	PCle Gen 1 Common Clock jitter (jitter limit = 86 ps)	F _{out} = 100 MHz	0.146		6.4	ps
J _{PCle1-SRNS}	PCle Gen 1 SRNS jitter		0.447		6.99	ps
J _{PCle2-cc}	PCle Gen 2 Common Clock jitter (jitter limit = 3 ps)		0.103		0.554	ps
J _{PCle2-SRNS}	PCle Gen 2 SRNS jitter		0.135		0.56	ps
J _{PCle3-cc}	PCle Gen 3 Common Clock jitter (jitter limit = 1 ps)		0.029		0.164	ps
J _{PCle3-SRNS}	PCle Gen 3 SRNS jitter		0.033		0.180	ps
J _{PCle4-cc}	PCle Gen 4 Common Clock jitter (jitter limit = 500 fs)		0.029		0.164	ps
J _{PCle4-SRNS}	PCle Gen 4 SRNS jitter		0.033		0.180	ps
J _{PCle5-cc}	PCle Gen 5 Common Clock jitter (jitter limit = 150 fs)		0.007		0.070	ps
J _{PCle5-SRNS}	PCle Gen 5 SRNS jitter		0.007		0.074	ps
J _{PCle6-cc}	PCle Gen 6 Common Clock jitter (jitter limit = 100 fs)		0.007		0.042	ps
J _{PCle6-SRNS}	PCle Gen 6 SRNS jitter		0.009		0.052	ps
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 156.25 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 156.25 MHz.		- 95		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 127		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 146		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 156		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 158		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 312.5 MHz		100	125	fs
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 312.5 MHz.		- 89		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 121		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 140		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 150		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 154		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 100 MHz		125	170	fs
		F _{out} = 125 MHz		100	125	fs
		F _{out} = 155.52 MHz		100	125	fs
		F _{out} = 161.1328125 MHz		110	150	fs
		F _{out} = 200 MHz		120	150	fs
		F _{out} = 400 MHz		100	135	fs
R _{PeriodJITT, RMS}	RMS Period Jitter	F _{out} ≥ 25 MHz		1.7		ps
R _{JITT, PK-PK}	Peak-peak Period Jitter	F _{out} ≥ 25 MHz		13		ps

over Recommended Operating Conditions, Typical Temp = 25°C, Frequency output = 156.25 MHz, VDD = 3.3 V, LVCMOS Output Capacitor load = 2.2 pF (unless otherwise specified)⁽⁷⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
LVCMOS - Clock Output Jitter						
R _J	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 156.25 MHz		0.25	0.5	ps
PN _{1k}	Phase Noise at 1 kHz Offset	F _{out} = 156.25 MHz		- 100		dBc/Hz
PN _{10k}	Phase Noise at 10 kHz Offset			- 128		dBc/Hz
PN _{100k}	Phase Noise at 100 kHz Offset			- 143		dBc/Hz
PN _{1M}	Phase Noise at 1 MHz Offset			- 150		dBc/Hz
PN _{10M}	Phase Noise at 10 MHz Offset			- 152		dBc/Hz
R _J	RMS Jitter (Integration BW: 12 kHz to 5 MHz)	F _{out} = 24 MHz		0.25	0.5	ps
		F _{out} = 25 MHz		0.25	0.5	ps
		F _{out} = 33.33 MHz		0.25	1	ps
	RMS Jitter (Integration BW: 12 kHz to 20 MHz)	F _{out} = 40 MHz		0.5	1	ps
		F _{out} = 50 MHz		0.4	1	ps
		F _{out} = 66.66 MHz		0.5	1	ps
		F _{out} = 74.25 MHz		0.3	0.5	ps
		F _{out} = 78 MHz		0.35	0.5	ps
		F _{out} = 100 MHz		0.35	0.5	ps
		F _{out} = 125 MHz		0.35	0.5	ps
RPeriodJITT _{,RMS}	RMS Period Jitter	F _{out} ≥ 25 MHz		1.5		ps
RJITT,PK-PK	Peak-peak Period Jitter	F _{out} ≥ 25 MHz		13		ps

- (1) DC Load condition
- (2) Measured using TI LMK6x Evaluation Module;
- (3) Refer to *Application Curves* section for Rise time and fall time details for different capacitor load values.
- (4) The Jitter specifications are based on design and characterization

6.8 Timing Diagrams

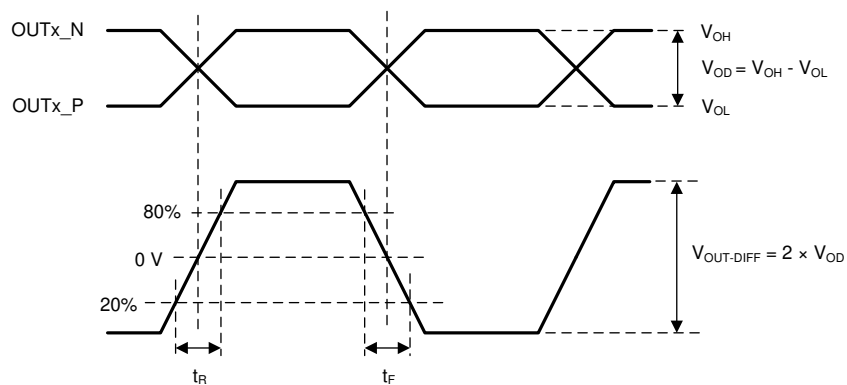


图 6-1. Differential Output Voltage and Rise/Fall Time

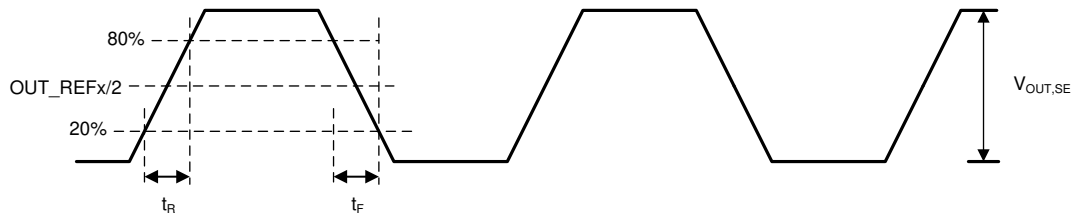


图 6-2. Single-Ended Output Voltage and Rise/Fall Time

6.9 Typical Characteristics

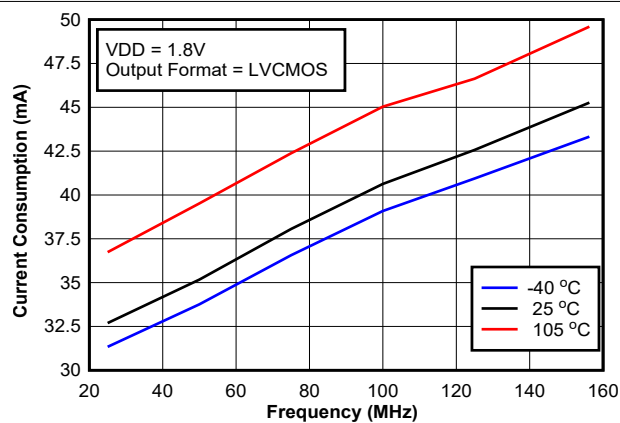


图 6-3. Current Consumption vs Frequency (LVCMOS, 1.8 V)

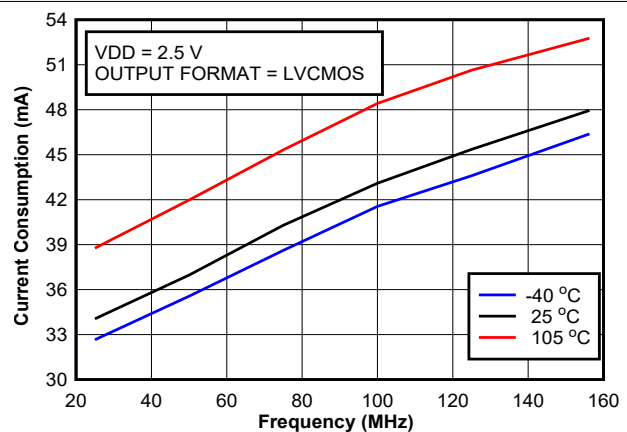


图 6-4. Current Consumption vs Frequency (LVCMOS, 2.5 V)

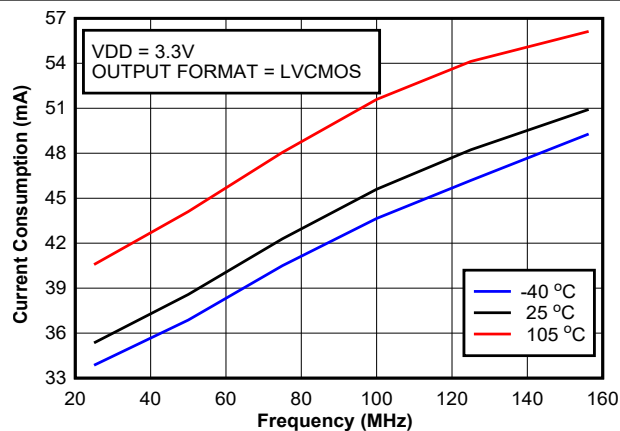


图 6-5. Current Consumption vs Frequency (LVCMOS, 3.3 V)

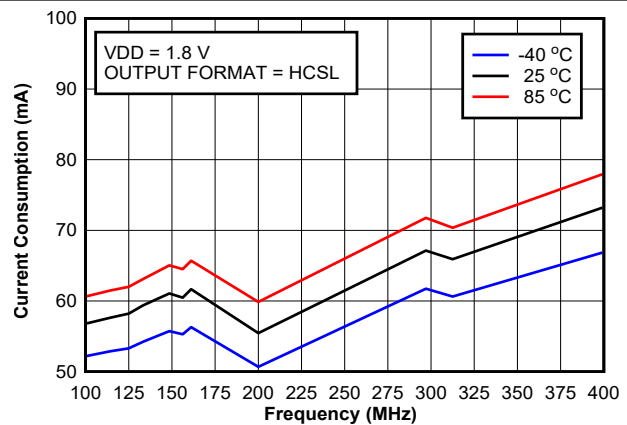


图 6-6. Current Consumption vs Frequency (HCSL, 1.8 V)

6.9 Typical Characteristics (continued)

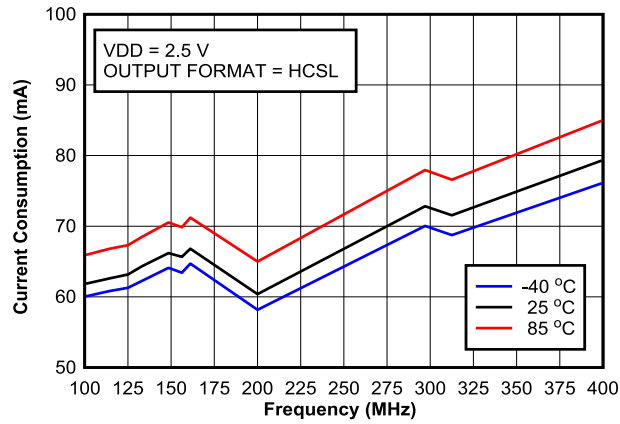


图 6-7. Current Consumption vs Frequency (HCSL, 2.5 V)

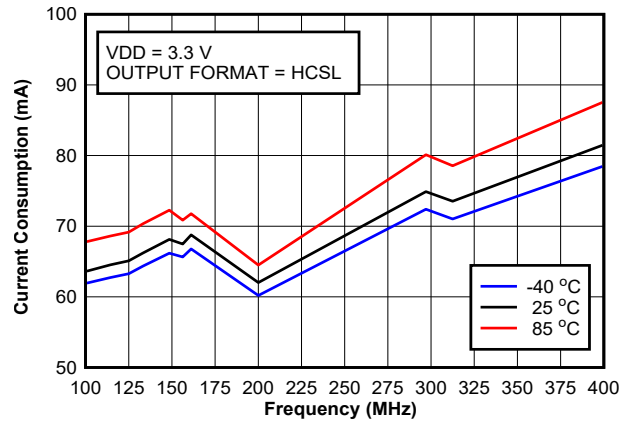


图 6-8. Current Consumption vs Frequency (HCSL, 3.3 V)

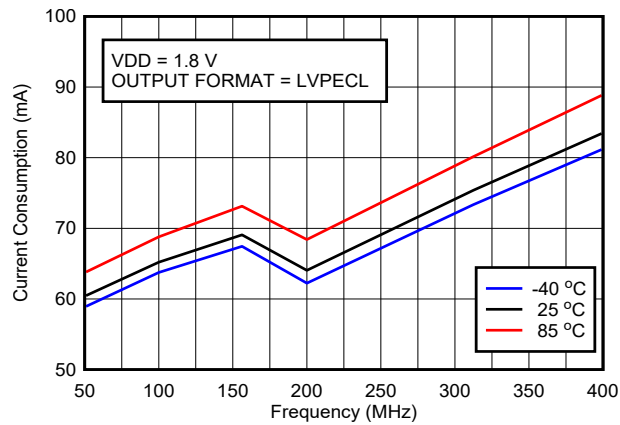


图 6-9. Current Consumption vs Frequency (LVPECL, 1.8 V)

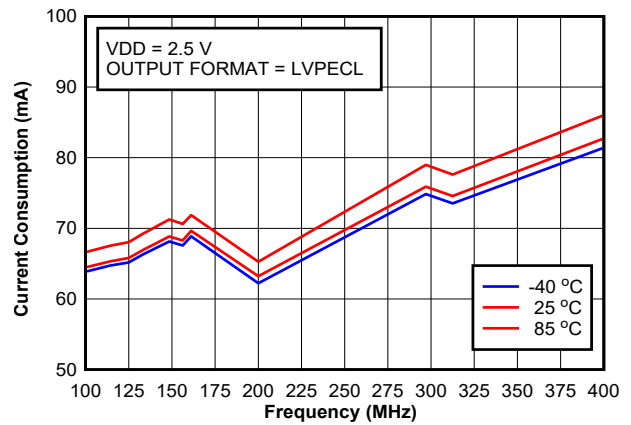


图 6-10. Current Consumption vs Frequency (LVPECL, 2.5 V)

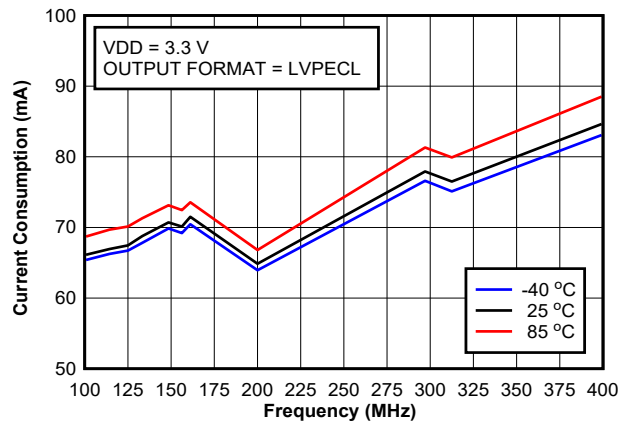


图 6-11. Current Consumption vs Frequency (LVPECL, 3.3 V)

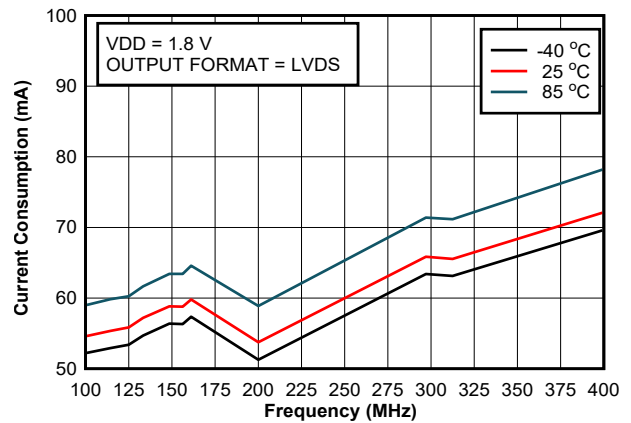


图 6-12. Current Consumption vs Frequency (LVDS, 1.8 V)

6.9 Typical Characteristics (continued)

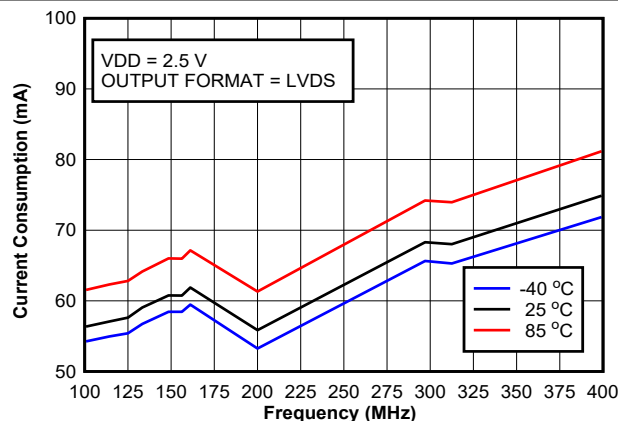


图 6-13. Current Consumption vs Frequency (LVDS, 2.5 V)

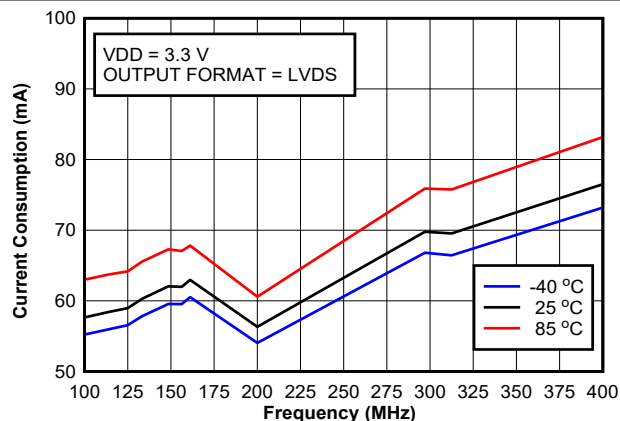


图 6-14. Current Consumption vs Frequency (LVDS, 3.3 V)

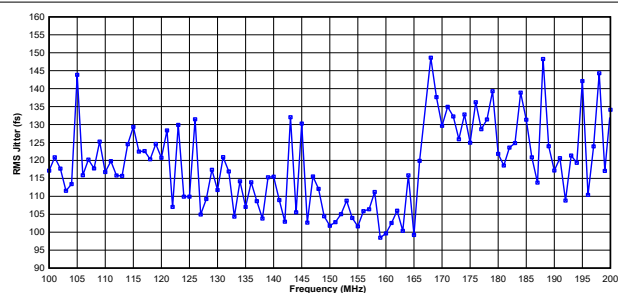


图 6-15. RMS Jitter vs Frequency (100 MHz to 200 MHz) for LVPECL, HCSL; TYPICAL 3.3 V, 25 °C

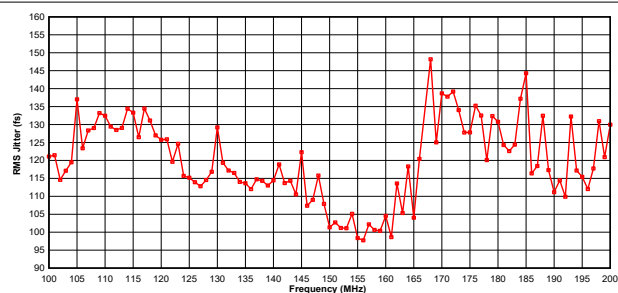


图 6-16. RMS Jitter vs Frequency (100 MHz to 200 MHz) for LVDS; TYPICAL 3.3 V, 25 °C

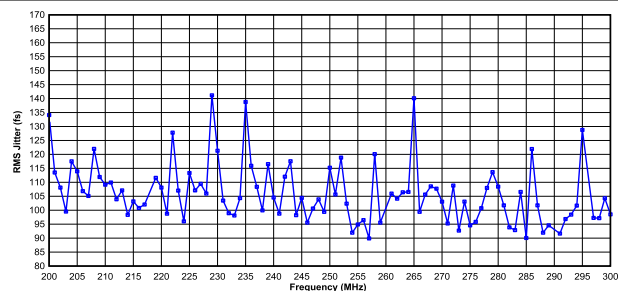


图 6-17. RMS Jitter vs Frequency (200 MHz to 300 MHz) for LVPECL, HCSL; TYPICAL 3.3 V, 25 °C

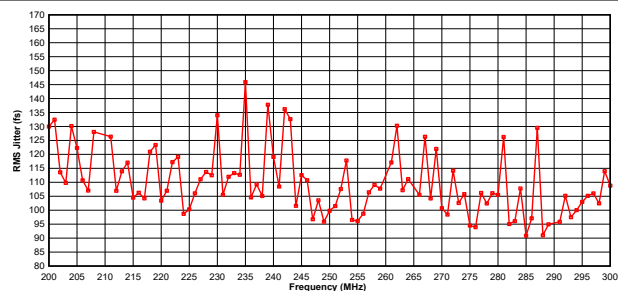


图 6-18. RMS Jitter vs Frequency (200 MHz to 300 MHz) for LVDS; TYPICAL 3.3 V, 25 °C

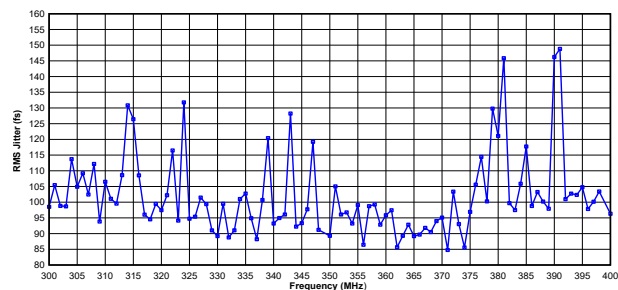


图 6-19. RMS Jitter vs Frequency (300 MHz to 400 MHz) for LVPECL, HCSL; TYPICAL 3.3 V, 25 °C

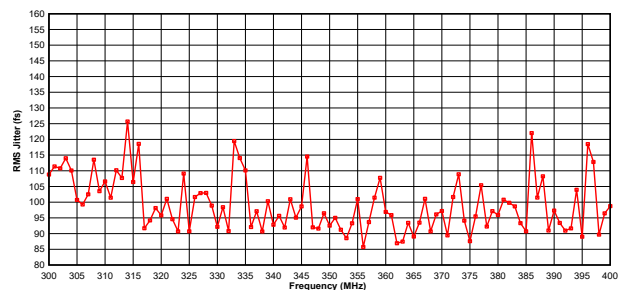


图 6-20. RMS Jitter vs Frequency (300 MHz to 400 MHz) for LVDS; TYPICAL 3.3 V, 25 °C

6.9 Typical Characteristics (continued)

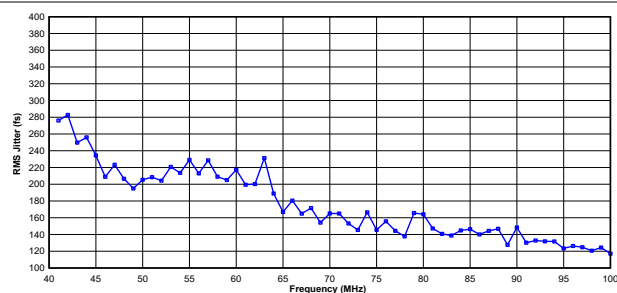


图 6-21. RMS Jitter vs Frequency (Below 100 MHz) for LVPECL, HCSL; TYPICAL 3.3 V, 25°C

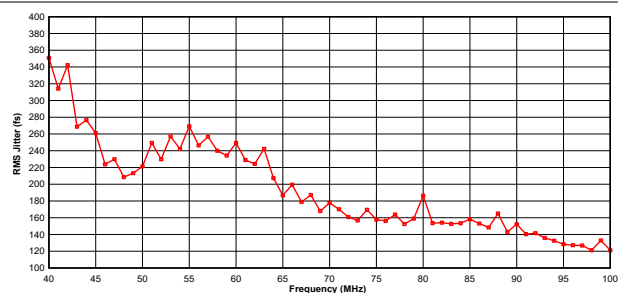


图 6-22. RMS Jitter vs Frequency (Below 100 MHz) for LVDS; TYPICAL 3.3 V, 25°C

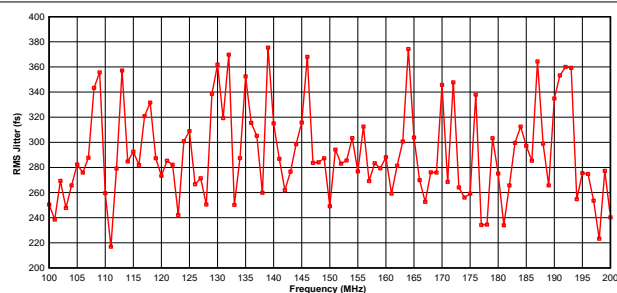


图 6-23. RMS Jitter vs Frequency (100 MHz - 200 MHz) for LVCMOS; TYPICAL 3.3 V, 25°C

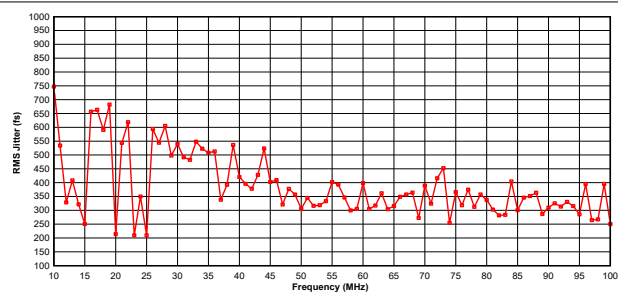


图 6-24. RMS Jitter vs Frequency (10 MHz - 100 MHz) for LVCMOS; TYPICAL 3.3 V, 25°C

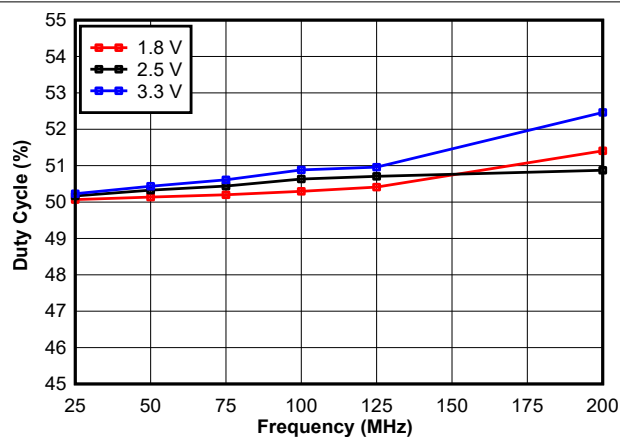


图 6-25. Duty Cycle (%) vs Frequency vs Power Supply; 25°C

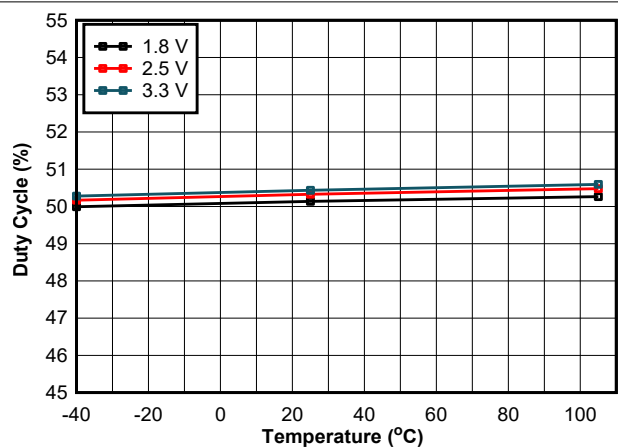


图 6-26. Duty Cycle (%) vs Temperature vs Power Supply; 50-MHz Frequency

6.9 Typical Characteristics (continued)

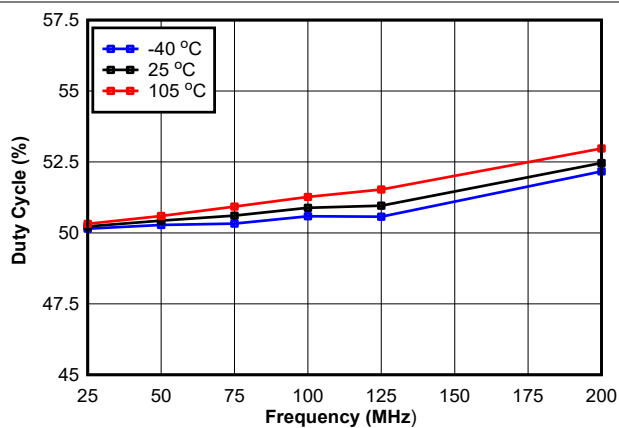


图 6-27. Duty Cycle (%) vs Frequency Over Temperature Range for LVCMOS; 3.3 V

7 Parameter Measurement Information

7.1 Device Output Configurations

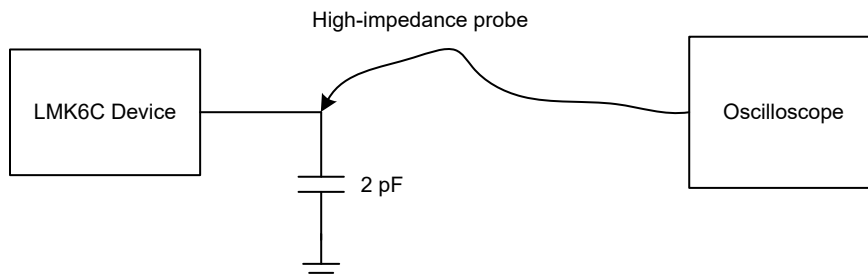


图 7-1. LMK6C Output Test Configuration

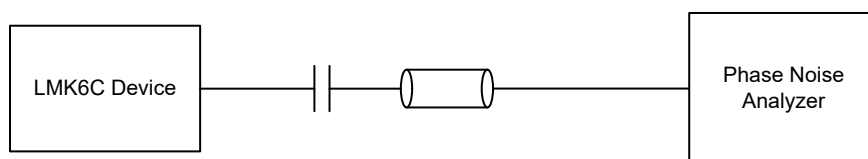


图 7-2. LMK6C Output Phase Noise Test Configuration

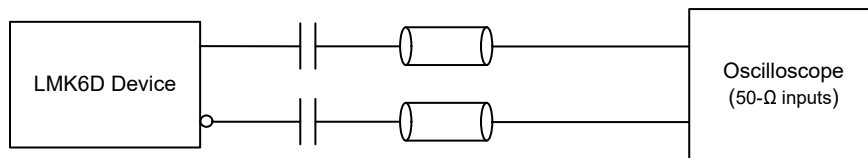


图 7-3. LMK6D Output Test Configuration

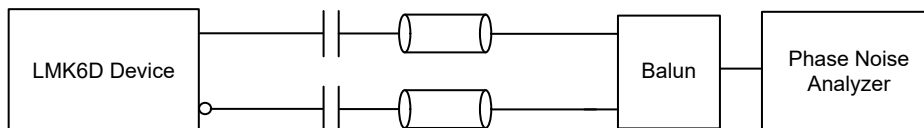


图 7-4. LMK6D Output Phase Noise Configuration

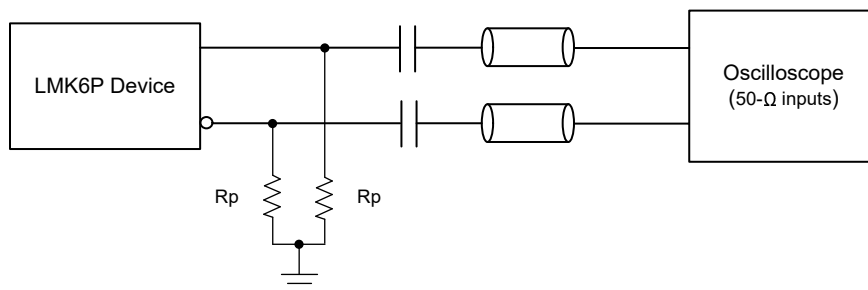


图 7-5. LMK6P Output Test Configuration

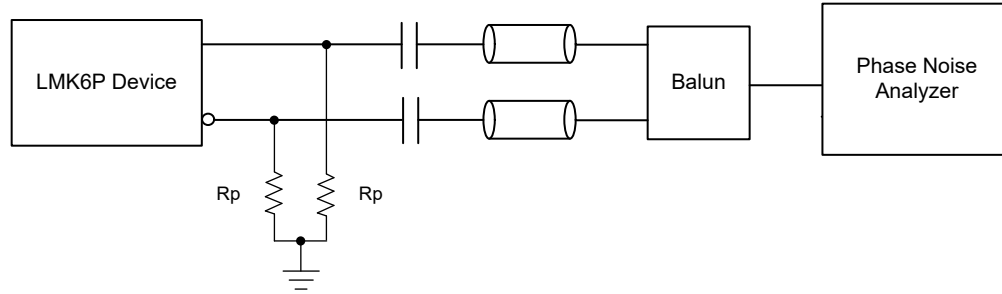


图 7-6. LMK6P Output Phase Noise Configuration

表 7-1. LMK6P Output Test configuration and Phase Noise Configuration Rp Values

SUPPLY (V)	Rp (Ω)
3.3 V	207.5
2.5 V	112.5
1.8 V	83.3

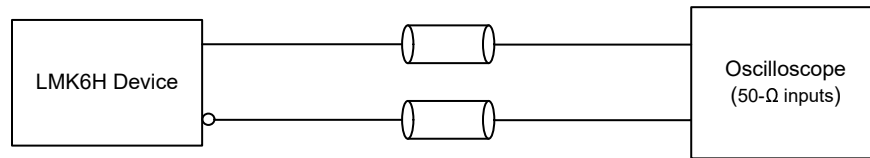


图 7-7. LMK6H Output Test Configuration

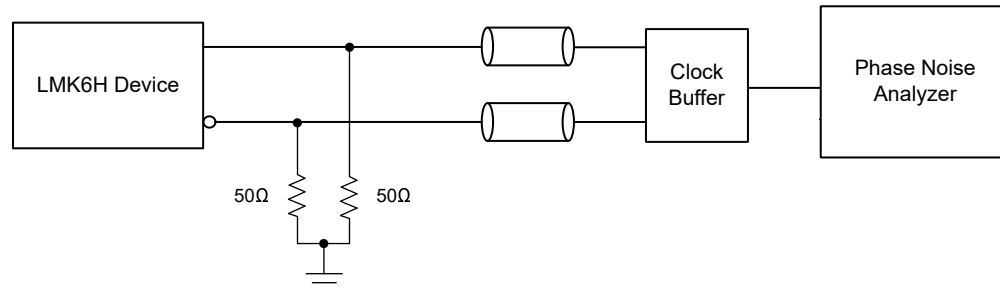


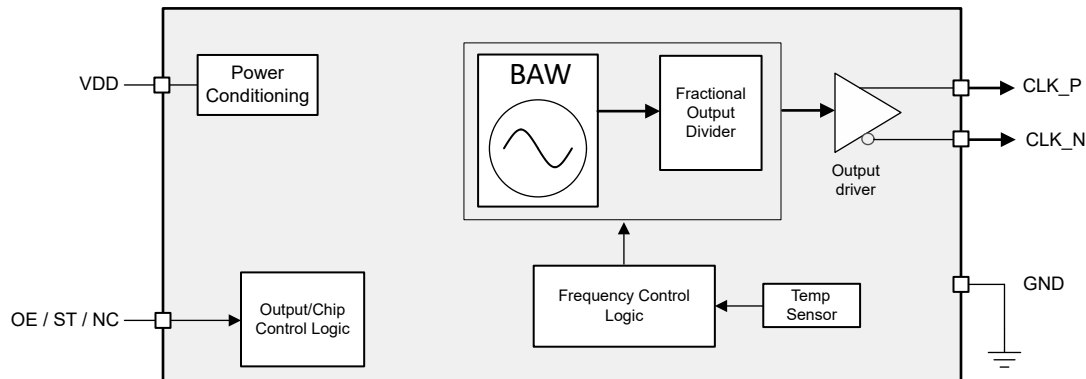
图 7-8. LMK6H Output Phase Noise Configuration

8 Detailed Description

8.1 Overview

The LMK6x is a fixed-frequency BAW based oscillator that can provide ultra-low jitter for both differential and single-ended output types.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Bulk Acoustic Wave (BAW)

TI's BAW resonator technology uses piezoelectric transduction to generate high-Q resonance at 2.5 GHz. The resonator is defined by the quadrilateral area overlaid by top and bottom electrodes. Alternating high- and low-acoustic impedance layers form acoustic mirrors beneath the resonant body to prevent acoustic energy leakage into the substrate. Furthermore, these acoustic mirrors are also placed on top of the resonator stack to protect the device from contamination and minimize energy leakage into the package materials. This unique dual-Bragg acoustic resonator (DBAR) allows efficient excitation without the need of costly vacuum cavities around the resonator. As a result, TI's BAW resonator is immune to frequency drift caused by adsorption of surface contaminants and can be directly placed in a non-hermetic plastic package with the oscillator IC in small standard oscillator footprints. Refer to [BAW](#) for more details on BAW technology.

8.3.2 Device Block-Level Description

The device contains a BAW oscillator, a Fractional Output Divider (FOD), and output driver, which together generates a pre-programmed output frequency. Temperature variations of oscillation frequency are continuously monitored by internal precision temperature sensor and provided as input to the frequency control logic block. Using this frequency control logic block, frequency corrections are performed internally for maintaining the output frequency within ± 25 ppm across temperature range and aging. The output driver is capable of providing both single-ended LVCMOS and differential LVPECL, LVDS, and HCSL output formats. The device contains an internal LDO which reduces the power supply noise, resulting in low noise clock output.

8.3.3 Function Pin(s)

Pin 1 on the LMK6C and pin 1 or pin 2 on the LMK6P, LMK6D, and LMK6H are the function pins which have multiple functions based on the orderable part number. The function can be used as Output Enable (OE), Stand By (ST) or No Connect (NC). Options for both Active High and Active Low are available for OE and ST. Contact TI for Active Low options. [表 8-1](#) lists the functions of pin 1 and pin 2 for differential output 6-pin packages and [表 8-2](#) lists the functions of pin 1 for single-ended outputs.

表 8-1. Function Pin Descriptions for 6-Pin Packages (LMK6D, LMK6H, LMK6P)

ORDERABLE OPTION	PIN DESCRIPTION	OUTPUT FUNCTION	OTHER FUNCTIONAL PIN CONFIGURATION
E (Pin 1)	Output Enable (Active High / NC)	HIGH or No Connect : Output active at Specified Frequency LOW : Output disabled, high impedance; current consumption is given by I_{DD-PD}	Pin 2 can be left floating or grounded
F (Pin 2)	Output Enable (Active High / NC)	HIGH or No Connect : Output active at Specified Frequency LOW : Output disabled, high impedance; current consumption is given by I_{DD-PD}	Pin 1 can be left floating or grounded
A (Pin 1)	Standby (Active Low)	LOW : High Impedance; standby mode; current consumption is given by standby current $I_{DD-STBY}$ HIGH or No Connect : Output active at Specified Frequency	Pin 2 can be left open or grounded
B (Pin 2)	Standby (Active Low)	LOW : High Impedance; standby mode; current consumption is given by standby current $I_{DD-STBY}$ HIGH or No Connect : Output active at Specified Frequency	Pin 1 can be left open or grounded

表 8-2. Function Pin Descriptions for 4-Pin Packages (LMK6C)

ORDERABLE OPTION	PIN DESCRIPTION	OUTPUT FUNCTION
E (Pin 1)	Output Enable (Active High / NC)	HIGH or No Connect : Output active at Specified Frequency LOW : Output disabled, high impedance; current consumption is given by I_{DD-PD}
A (Pin 1)	Standby (Active Low)	LOW : High Impedance; standby mode; current consumption is given by standby current $I_{DD-STBY}$ HIGH or No Connect : Output active at Specified Frequency

In standby mode, all blocks are powered down to provide a maximum current consumption savings equivalent to the standby current provided in the *Current Consumption Characteristics* portion of the [Electrical Characteristics](#) table. The return to the output clock active time corresponds to same as the initial start-up time.

The Function Pin is driven internally with resistance $>100\text{ k}\Omega$.

8.3.4 Clock Output Interfacing and Termination

These figures show the recommended output interfacing and termination circuits.

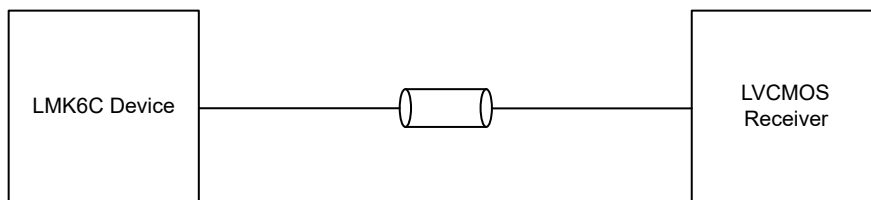


图 8-1. LMK6C Output to LVCMOS Receiver

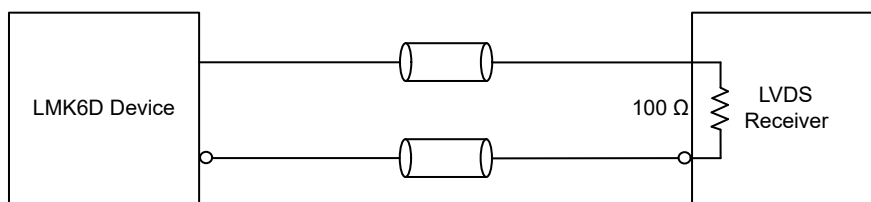


图 8-2. LMK6D Output DC-Coupled to LVDS Receiver With Internal Termination/Biasing

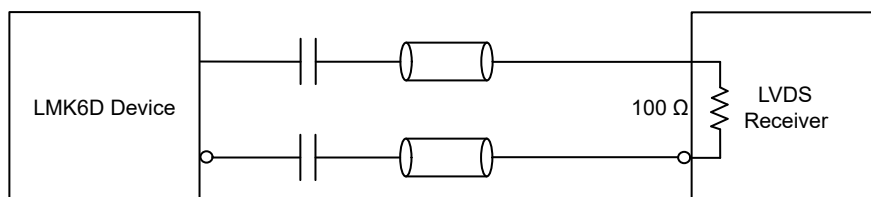


图 8-3. LMK6D Output AC Coupled to LVDS Receiver With Internal Termination/Biasing

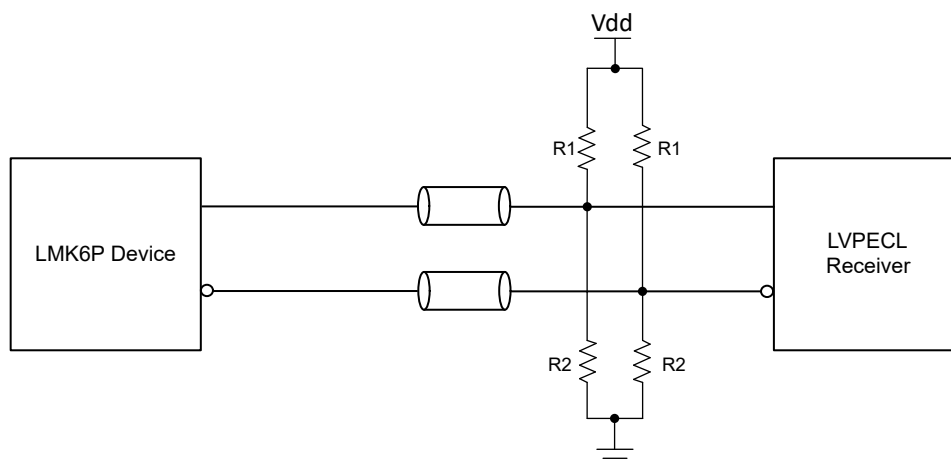


图 8-4. LMK6P Output DC-Coupled to LVPECL Receiver With External Termination/Biasing (T-Network)

表 8-3. LMK6P T-Network DC-Coupled Resistor Values

SUPPLY (V)	R1 (Ω)	R2 (Ω)
3.3	133	82
2.5	250	62.5
1.8	450	56.5

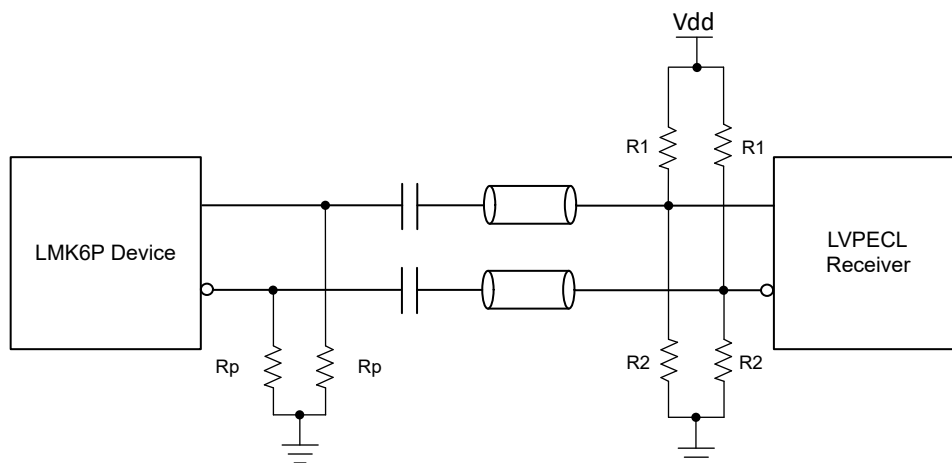


图 8-5. LMK6P Output AC-Coupled to LVPECL Receiver With External Termination/Biasing (T-Network)

表 8-4. LMK6P T-Network AC-Coupled Resistor Values

SUPPLY (V)	Rp (Ω)	R1 (Ω)	R2 (Ω)
3.3	207.5	133	82
2.5	112.5	250	62.5
1.8	83.3	450	56.6

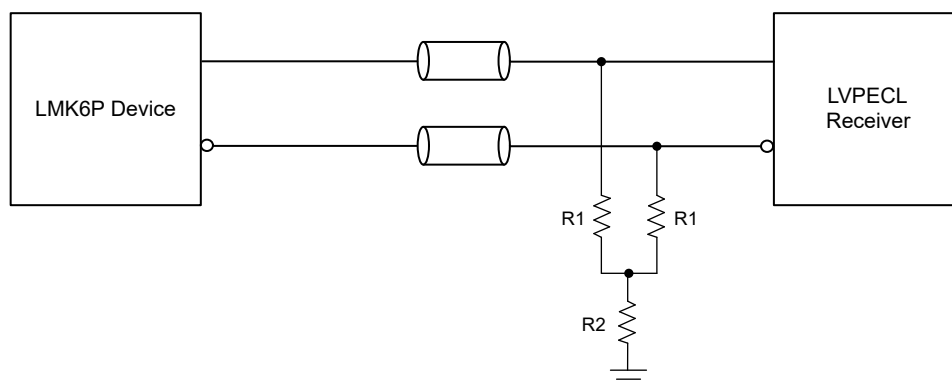


图 8-6. LMK6P Output DC-Coupled to LVPECL Receiver With External Termination/Biasing (Y-Network)

表 8-5. LMK6P Y-Network DC-Coupled Resistor Values

SUPPLY (V)	R1 (Ω)	R2 (Ω)
3.3	50	78.8
2.5	50	31.3
1.8	50	16.7

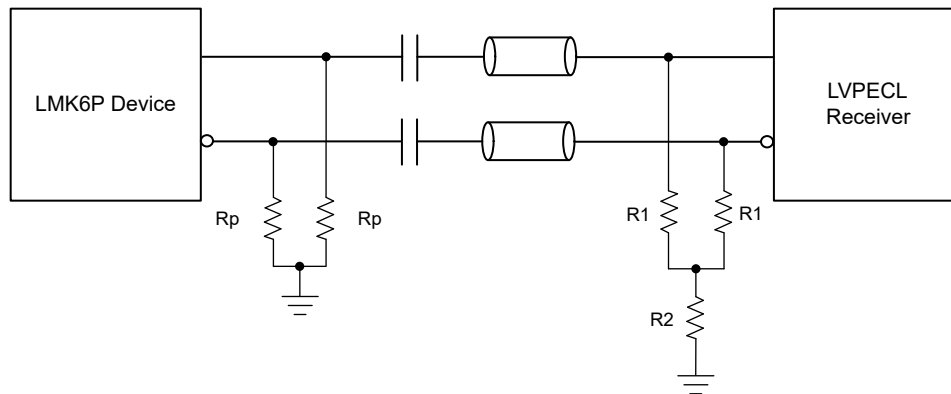


图 8-7. LMK6P Output AC-Coupled to LVPECL Receiver With External Termination/Biasing (Y-Network)

表 8-6. LMK6P Y-Network AC-Coupled Resistor Values

SUPPLY (V)	Rp (Ω)	R1 (Ω)	R2 (Ω)
3.3	207.5	50	78.8
2.5	112.5	50	31.3
1.8	83.3	50	16.7

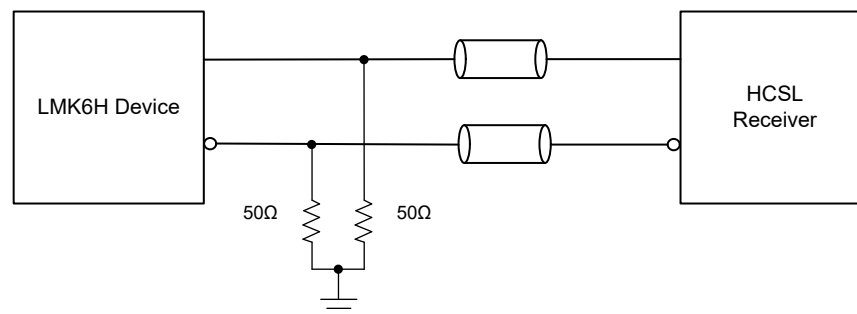


图 8-8. LMK6H Output to HCSL Receiver With External Termination

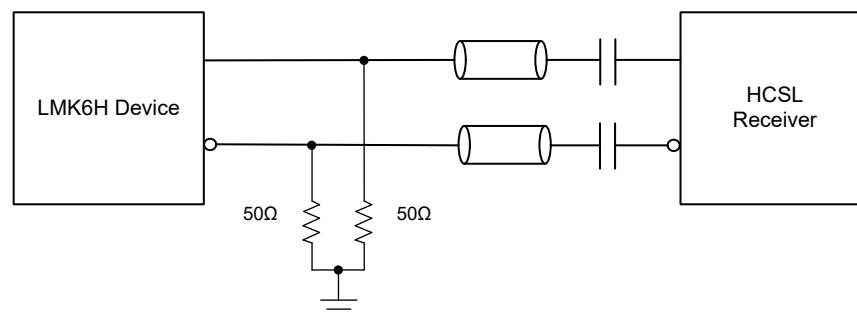


图 8-9. LMK6H Output AC-Coupled to HCSL Receiver With External Termination

8.3.5 Temperature Stability

图 8-10 shows the frequency variation of the LMK6x differential output oscillator over the temperature range of -40°C to 85°C for total of 60 units. 图 8-11 shows the frequency variation of the LMK6C single-ended output oscillator over the operating temperature range of -40°C to 105°C . These plots represent the typical

temperature stability of the device, remaining below ± 10 ppm. The devices are soldered onto the evaluation board as per the standard soldering profile and frequency variation measurements are carried out. The output frequency is 156.25 MHz for these tests.

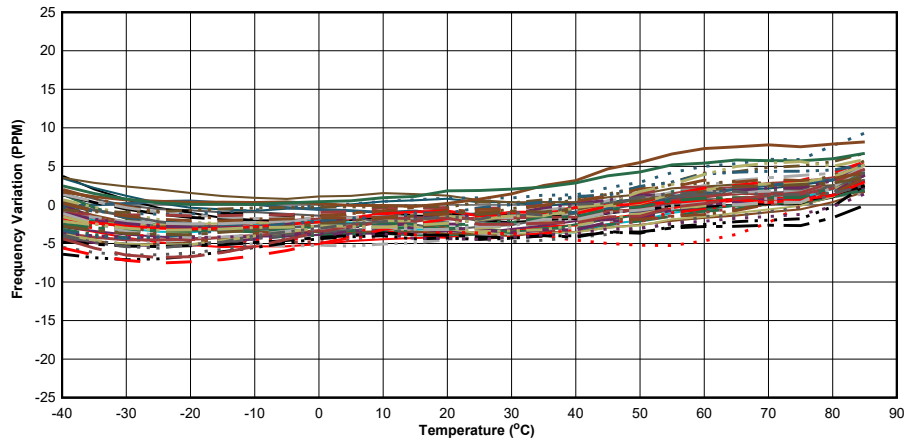


图 8-10. Frequency Change Over Temperature (LMK6x Differential Output Device)

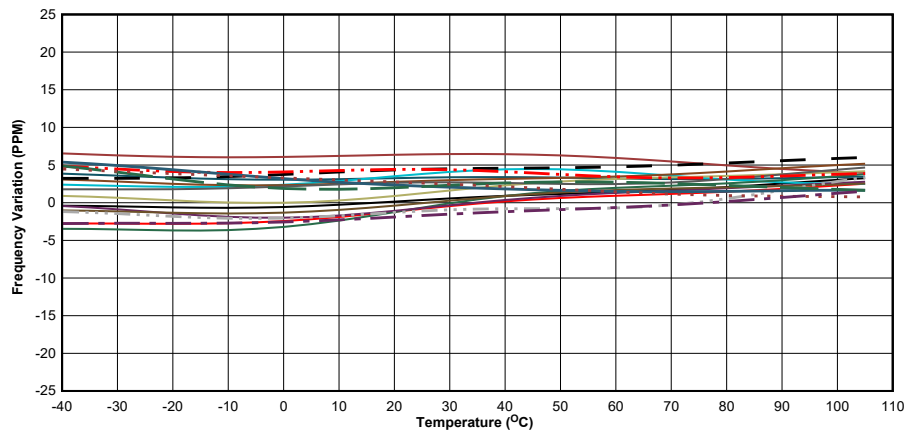


图 8-11. Frequency Change Over Temperature (LMK6C Single-Ended Output Device)

8.3.6 Mechanical Robustness

For reference oscillators, vibration and shock are common causes for increased phase noise and jitter, frequency shift and spikes, or even physical damages to the resonator and the package. Compared to quartz crystals, the BAW resonator is more immune to vibration and shock due to its orders of magnitude, smaller mass, and higher frequency, which means force applied to the device from acceleration is much smaller due to smaller mass.

图 8-12 shows the LMK6x BAW oscillator vibration performance. In this test, the LMK6x oscillator mounted on an EVM is subject to 10g acceleration force, ranging from 50 Hz to 2 kHz in x, y, and z-axis. Phase noise trace with spur due to vibration is captured using Keysight E5052B and frequency deviation is calculated from the spur power. Then the frequency deviation is converted to ppb by noting the carrier frequency and normalized to ppb/g. Finally, the RMS sum of ppb/g along all three axes is reported as the Vibration sensitivity in ppb/g. LMK6x performance under vibration is approximately 2 ppb/g while most quartz oscillators best case is 3 ppb/g and worse can be above 10 ppb/g.

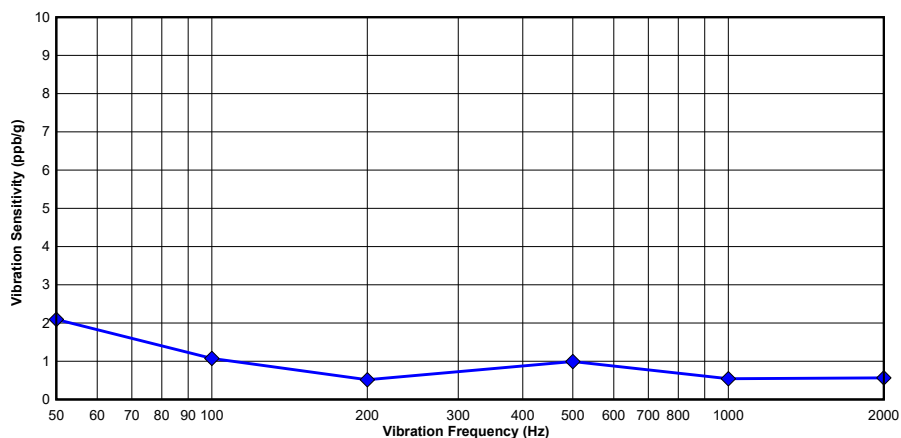


图 8-12. LMK6X BAW Oscillator Vibration Performance

8.4 Device Functional Modes

The LMK6x BAW Oscillator is a fixed output frequency device and does not require any programming. The device pin 1 (and pin 2 for a 6-pin device) has different functions. See the [Function Pin\(s\)](#) section for more information on the function pins.

9 Application and Implementation

备注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The LMK6x is high-performance, fixed-frequency oscillator that can be used as a reference clock. The product family supports any output frequency between 1 MHz to 400 MHz for differential LMK6D, LMK6H, LMK6P or 1 MHz to 200 MHz for singled-ended LVCMOS clock output types, and 1.8-V or 2.5-V through 3.3-V supply rails.

9.2 Typical Application

For reference schematic implementation for LMK6x family of oscillators, refer to the [LMK6EVM User's Guide](#) for bypass capacitor and AC-coupling capacitor value recommendations. Refer to the [Clock Output Interfacing and Termination](#) section for output clock required termination and biasing.

图 9-1 shows a typical application example. The LMK6D differential oscillator is used as an input to the LVDS buffer input in this example.

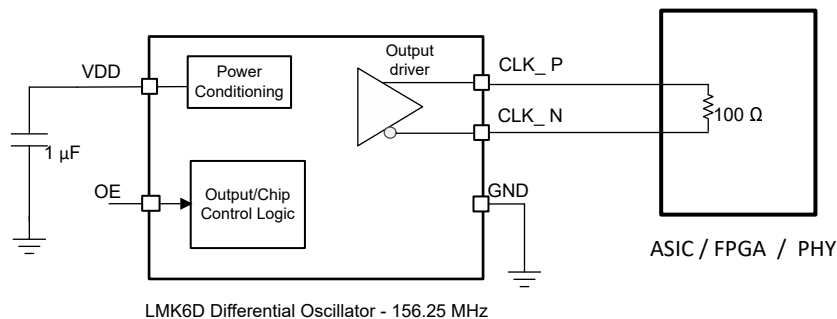


图 9-1. Application Example

9.2.1 Design Requirements

The LMK6x is a fixed-frequency oscillator with no programming needed. Make sure to follow the recommended termination options as described in the [Clock Output Interfacing and Termination](#) section closely. Refer to the [Function Pin\(s\)](#) section to understand the pin 1 and pin 2 functions, and order the part number as per your requirements for Output Enable (OE), Standby (ST) options.

9.2.2 Detailed Design Procedure

The LMK6x has three different options for differential output which are LVDS, LVPECL, HCSL type and one LVCMOS single-ended output type. For designing with the any of the oscillator output type in actual system, use the proper AC or DC termination based on the application requirement. Refer to the [Clock Output Interfacing and Termination](#) section for the details of all the AC and DC termination schemes and use the appropriate option. The figures in this section have all the AC and DC coupling options with the termination resistor values. The LMK6x has an integrated LDO and has excellent PSRR performance as shown in the [Electrical Characteristics](#) table. Refer to the LMK6EVM for the reference layout recommendation while designing the LMK6x BAW oscillator.

For the Function Pin 1 of LMK6C, connect typical 10-k Ω or less resistor to VDD for driving the OE pin High. Note this pin can be left open if you do not want to use pullup resistor as the device has > 100-k Ω internal pullup resistor. For driving the OE pin to Low, use the typical 10 k Ω or less resistor as a pulldown resistor. For the

Function Pin 1 or Functional Pin 2 for LMK6D, LMK6H, LMK6P, you can use the similar approach described for LMK6C.

9.2.3 Application Curves

The LMK6C LVCMOS output connects to different load capacitances based on the actual application use case in a system. With the different load capacitance, the rise time / fall time varies for the specific output frequency. The following graphs shows the Rise / Fall time for load capacitance of 2.2 pF, 4.7 pF, 10 pF, 15 pF and 22 pF for temperature range from -40°C to 105°C.

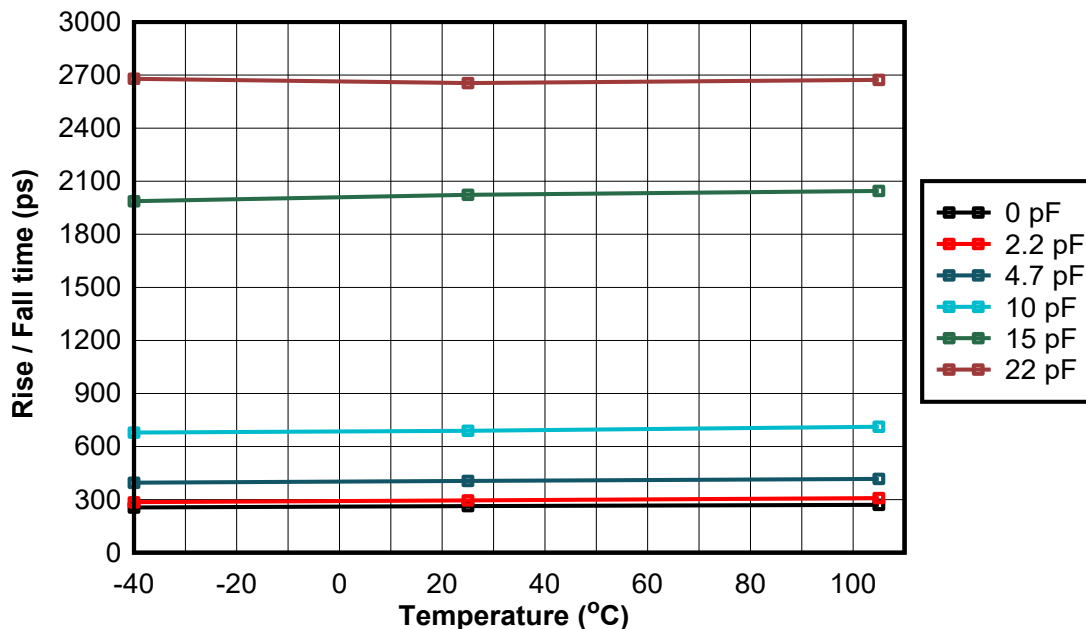


图 9-2. Rise / Fall time (ps) vs Temperature for 25-MHz Output Frequency, 3.3-V Supply

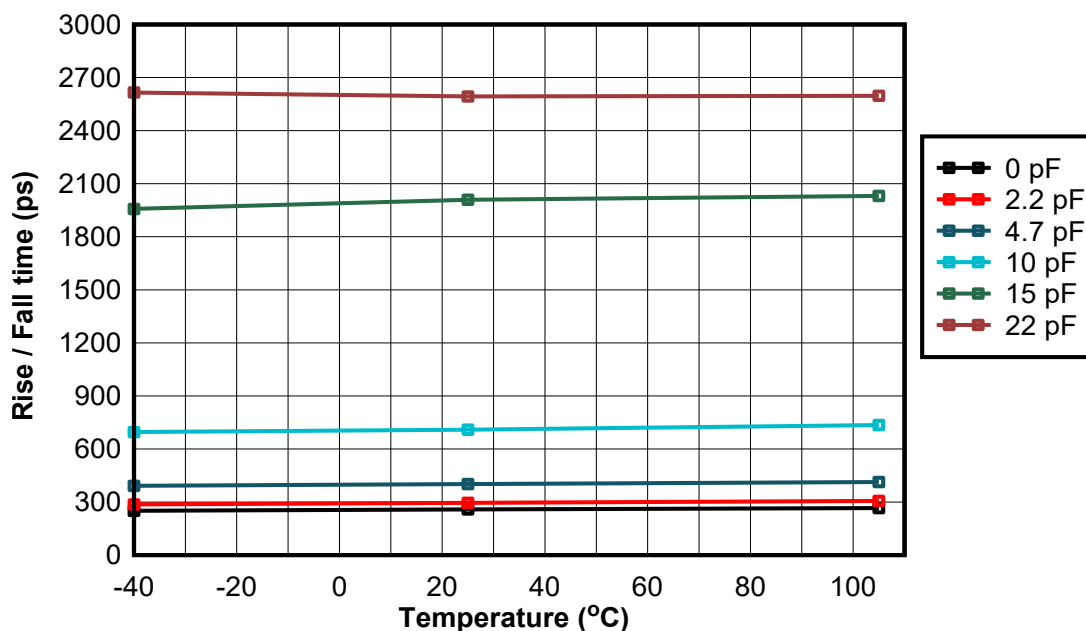


图 9-3. Rise / Fall time (ps) vs Temperature for 50-MHz Output Frequency, 3.3-V Supply

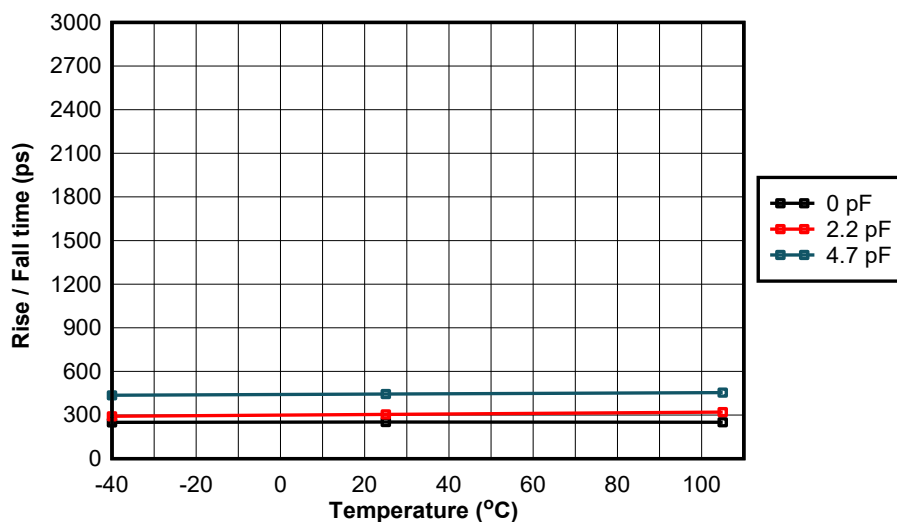


图 9-4. Rise / Fall time (ps) vs Temperature for 100-MHz Output Frequency, 3.3-V Supply

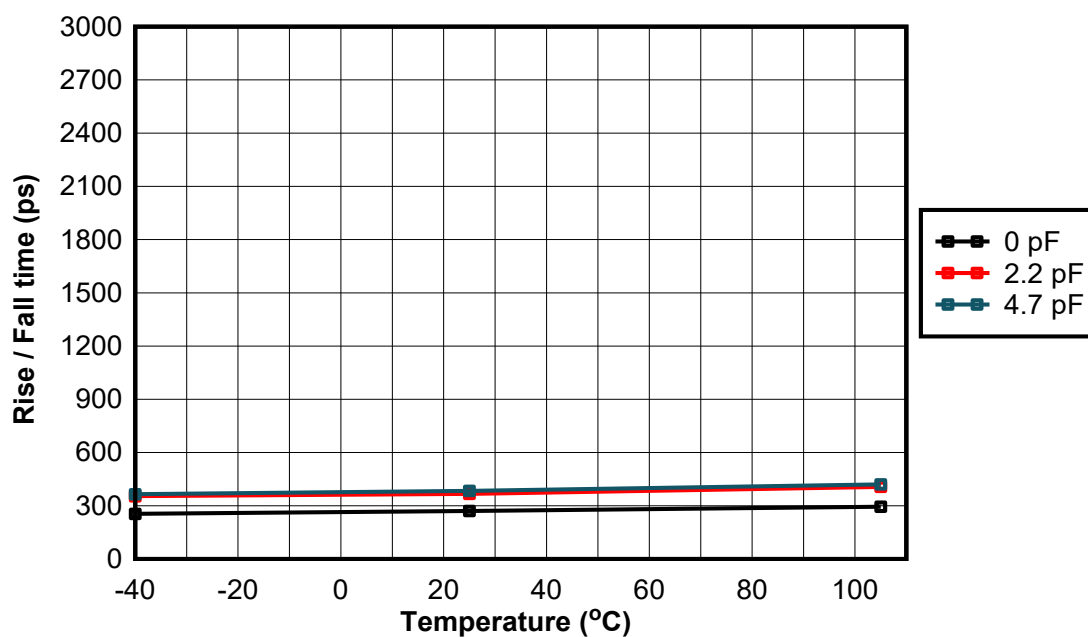


图 9-5. Rise / Fall time (ps) vs Temperature for 200-MHz Output Frequency, 3.3-V Supply

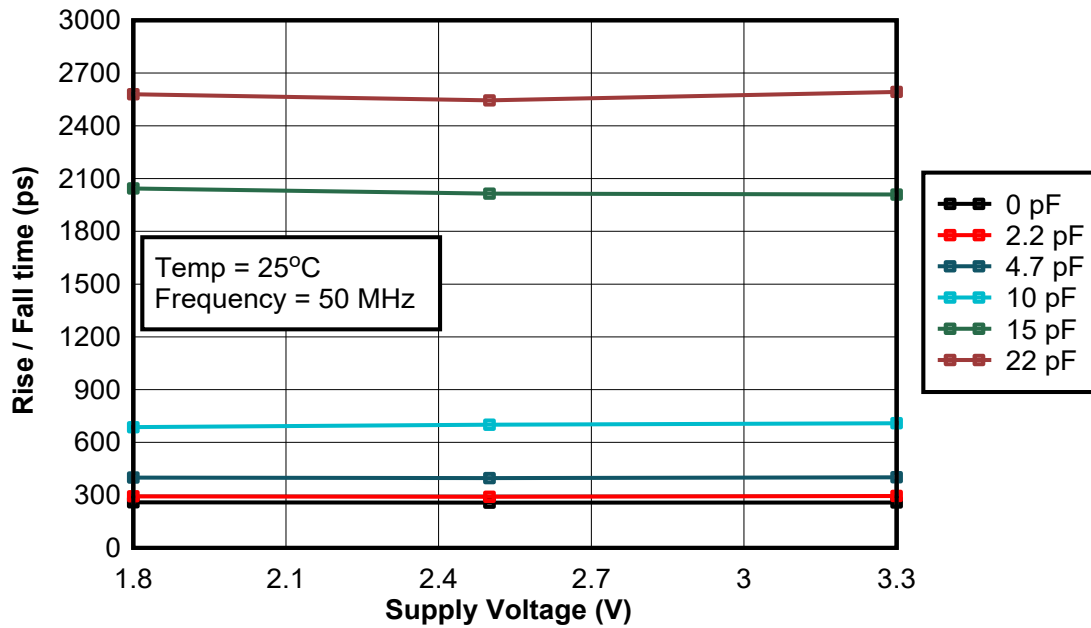


图 9-6. Rise / Fall time (ps) vs Supply Voltage vs Load Capacitance

9.3 Power Supply Recommendations

For the best electrical performance of the LMK6x, TI recommends use 1 μ F capacitor on the device power supply bypass network. TI also recommends using component side mounting of the power-supply bypass capacitors, and best to use 0201 or 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low impedance connection to the ground plane.

9.4 Layout

9.4.1 Layout Guidelines

The following sections provide recommendations for board layout, solder reflow profile and power-supply bypassing when using the LMK6x to ensure good thermal and electrical performance and signal integrity of the entire system.

9.4.1.1 Ensuring Thermal Reliability

The LMK6x is a high-performance device. Therefore, pay careful attention to device configuration and printed circuit board (PCB) layout with respect to power consumption. The ground pin must be connected to the ground plane of the PCB through three vias or more to maximize thermal dissipation out of the package.

The equation below describes the relationship between the PCB temperature around the LMK6x and its junction temperature.

$$T_B = T_J - \Psi_{JB} \times P \quad (1)$$

where

- T_B : PCB temperature around the LMK6x
- T_J : Junction temperature of LMK6x
- Ψ_{JB} : Junction-to-board thermal resistance parameter of LMK6x (refer to the *Thermal Information* tables in the [Specifications](#) section for this information)
- P: On-chip power dissipation of LMK6x

9.4.1.2 Recommended Solder Reflow Profile

TI recommends following the solder paste supplier's recommendations to optimize flux activity and to achieve proper melting temperatures of the alloy within the guidelines of J-STD-20. It is preferable for the LMK6x to be processed with the lowest peak temperature possible while also remaining below the components peak temperature rating as listed on the MSL label. The exact temperature profile would depend on several factors including maximum peak temperature for the component as rated on the MSL label, Board thickness, PCB material type, PCB geometries, component locations, sizes, densities within PCB, as well solder manufactures recommended profile, and capability of the reflow equipment to as confirmed by the SMT assembly operation.

9.4.2 Layout

Refer to the [LMK6EVM User's Guide](#) for printed circuit board layout examples for LMK6D, LMK6H, LMK6P and LMK6C devices. The figured below show the PCB layout example as done on the evaluation module for the LMK6x EVM.

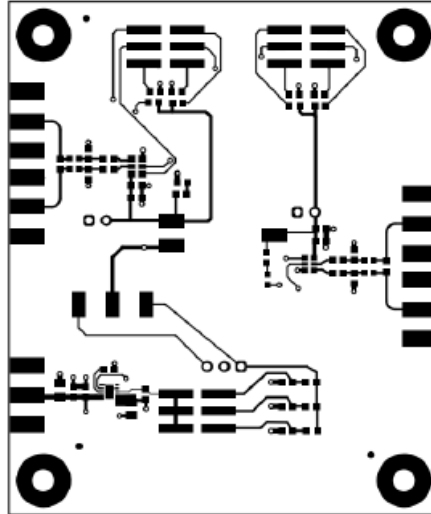


图 9-7. PCB Layout Example From LMK6 EVM - Top Layer

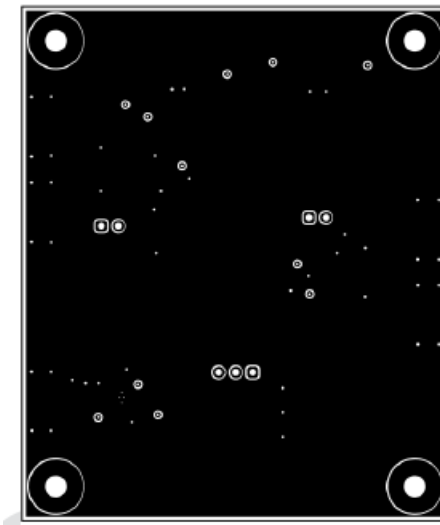


图 9-8. PCB Layout Example From LMK6 EVM - GND Layer 1

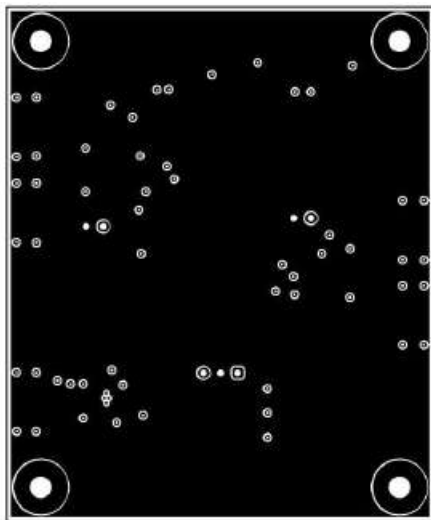


图 9-9. PCB Layout Example From LMK6 EVM - GND Layer 2

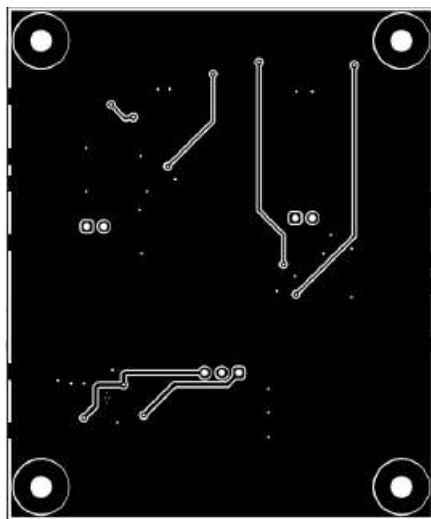


图 9-10. PCB Layout Example From LMK6 EVM - Bottom Layer

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [LMK6EVM User's Guide](#)
- Texas Instruments, [Standalone BAW Oscillators Advantages Over Quartz Oscillators application note](#)
- Texas Instruments, [BAW oscillator solutions for Building Automation application note](#)
- Texas Instruments, [BAW oscillator solutions for Factory Automation application note](#)
- Texas Instruments, [BAW oscillator solutions for Grid Infrastructure application note](#)
- Texas Instruments, [BAW oscillator solutions for Optical Modules application note](#)

10.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](#) 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

TI E2E™ 中文支持论坛 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

10.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

11 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (February 2023) to Revision E (January 2024)	Page
• 向标准频率列表添加了值.....	1
• Changed the part number guides in the <i>Device Ordering Information</i> section.....	3

Changes from Revision C (December 2022) to Revision D (February 2023)	Page
• Changed the NO. column to DLE/DLF in the <i>Pin Functions</i> table for the DLF package release.....	5

Changes from Revision B (November 2022) to Revision C (December 2022)	Page
• 将数据表状态从“预告信息”更改为“量产数据”	1
• 从 LMK6D、LMK6H 和 LMK6P 器件中删除了预发布说明.....	1

12 Mechanical, Packaging, and Orderable Information

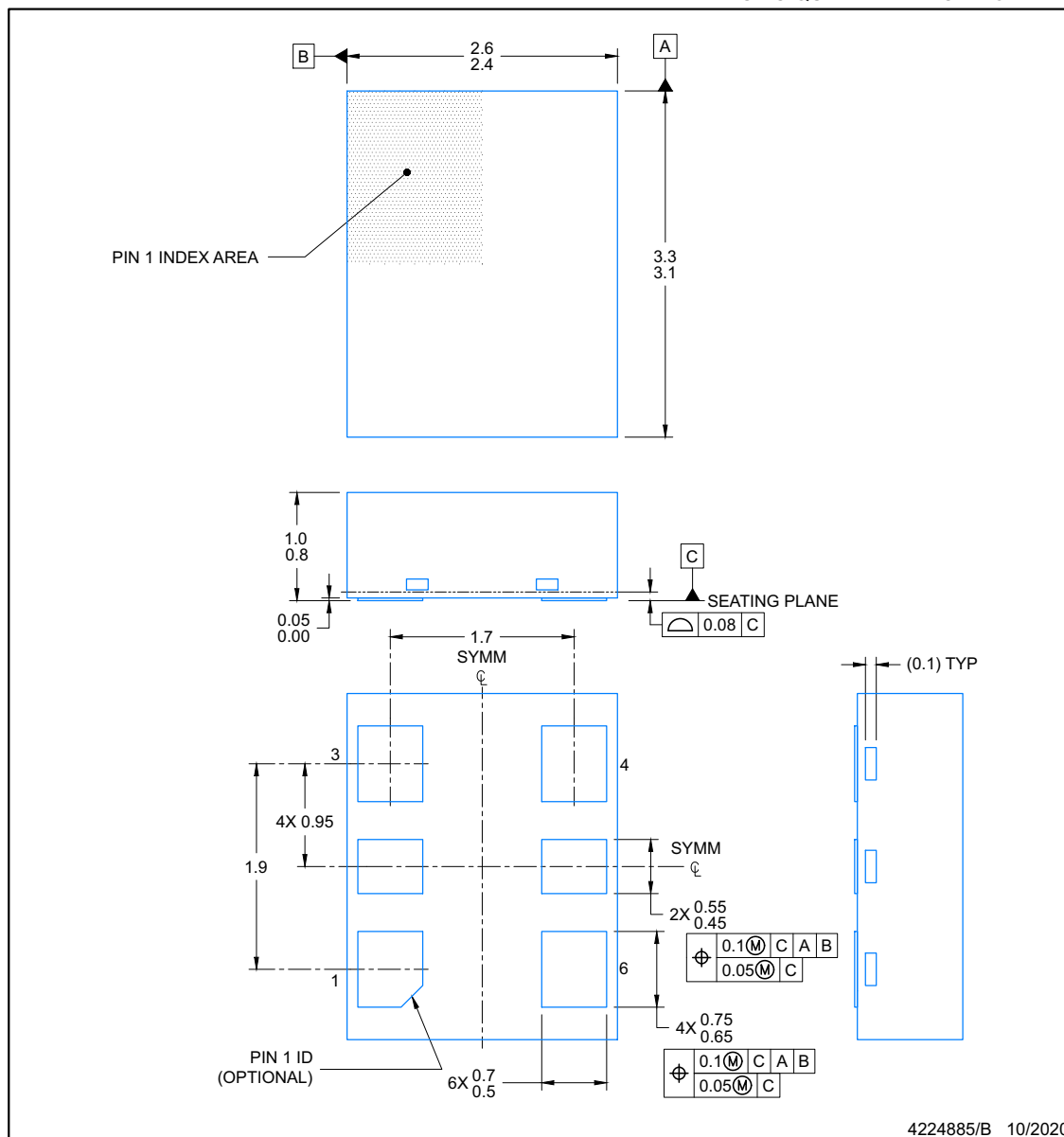
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

DLE0006A

PACKAGE OUTLINE

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

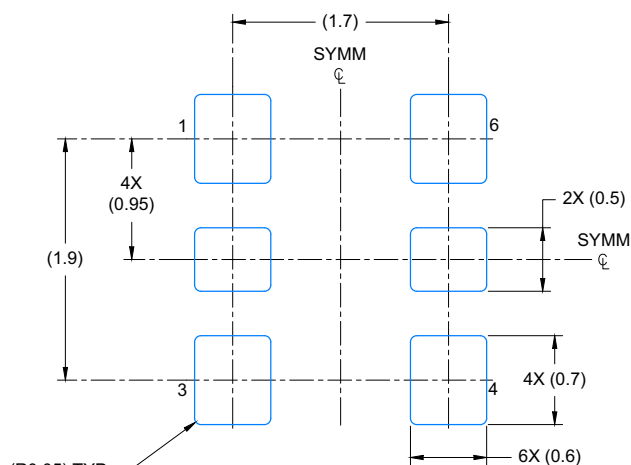
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

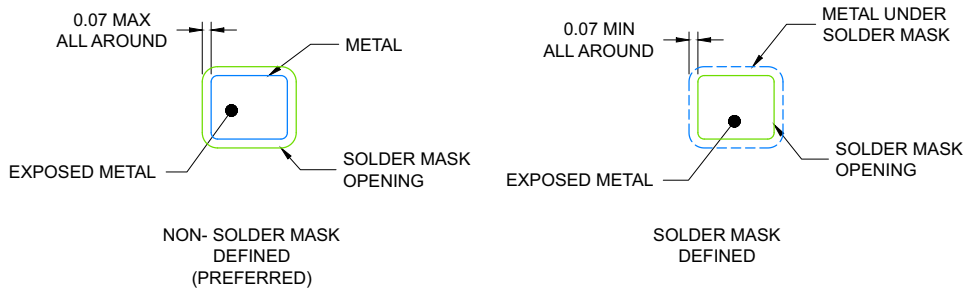
VSON - 1 mm max height

DLE0006A

PLASTIC QUAD FLAT PACK-NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



SOLDER MASK DETAILS

4224885/B 10/2020

NOTES: (continued)

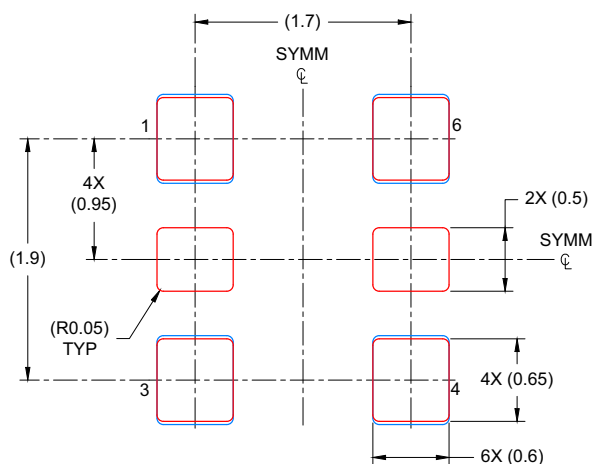
- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271) .

EXAMPLE STENCIL DESIGN

DLE0006A

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
PADS 1,3,4 & 6: 93%
SCALE: 20X

4224885/B 10/2020

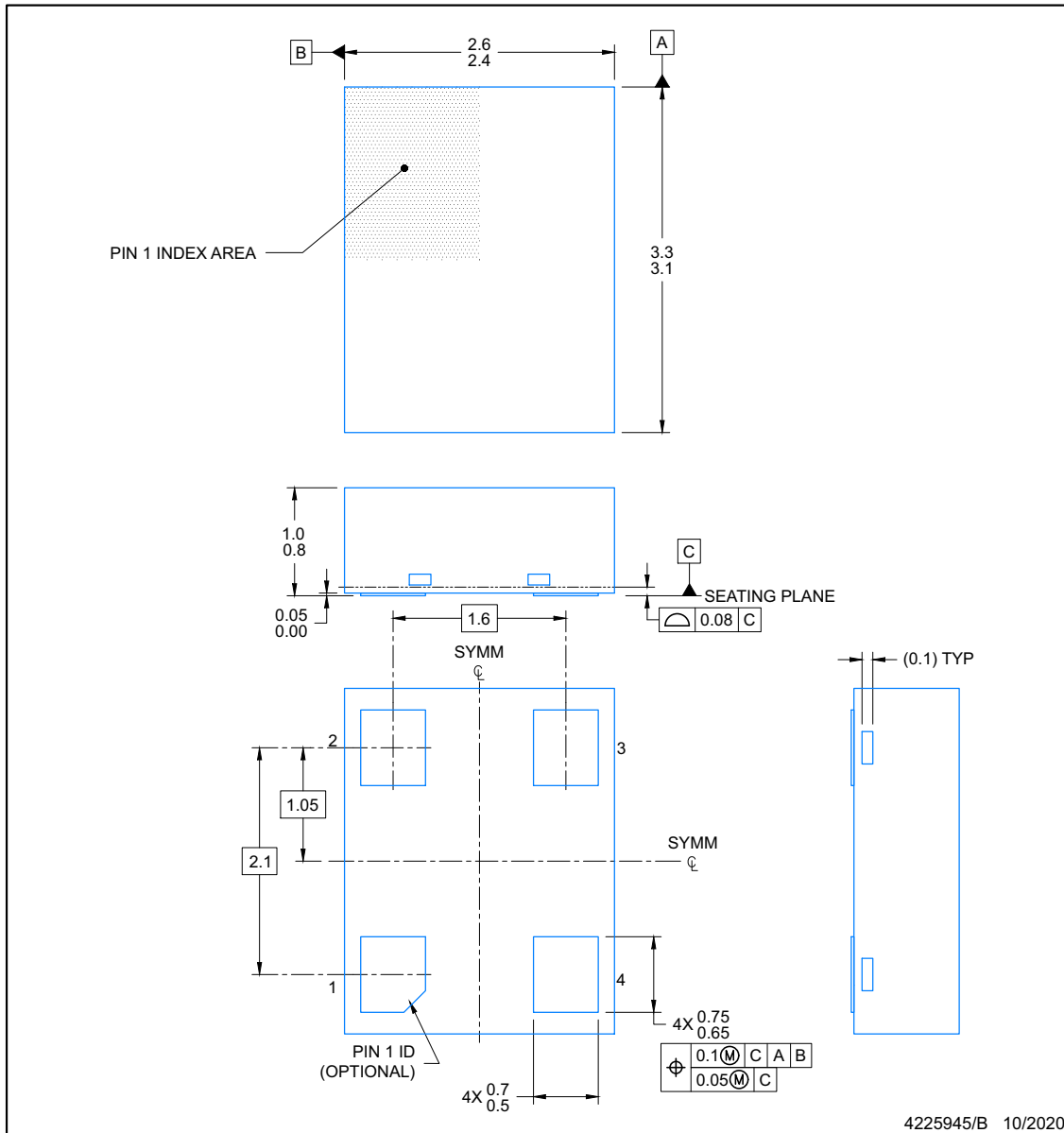
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DLE0004A

PACKAGE OUTLINE VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

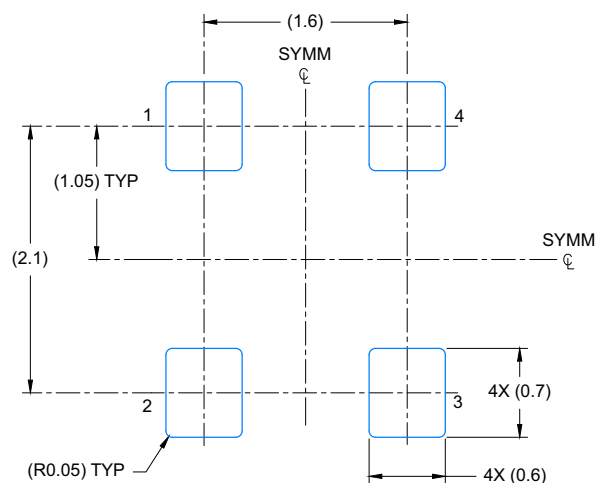
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

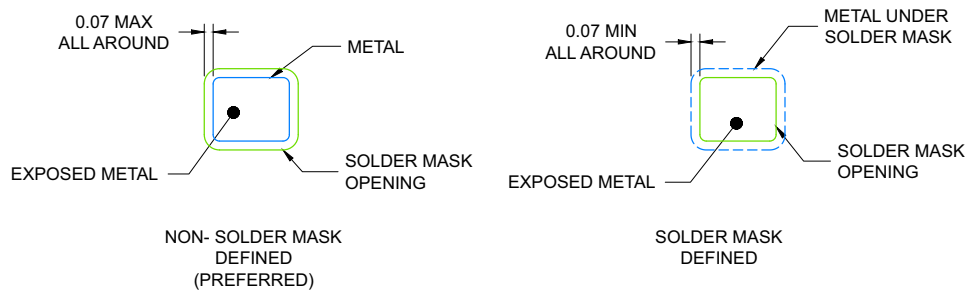
VSON - 1 mm max height

DLE0004A

PLASTIC QUAD FLAT PACK-NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



SOLDER MASK DETAILS

4225945/B 10/2020

NOTES: (continued)

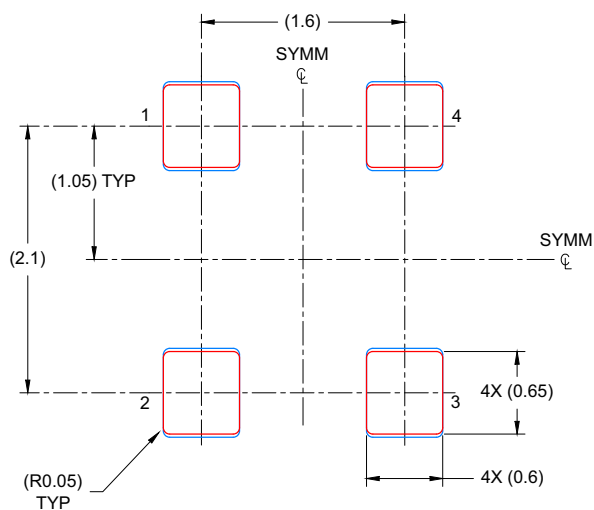
- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271) .

EXAMPLE STENCIL DESIGN

DLE0004A

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
ALL PADS: 93%
SCALE: 20X

4225945/B 10/2020

NOTES: (continued)

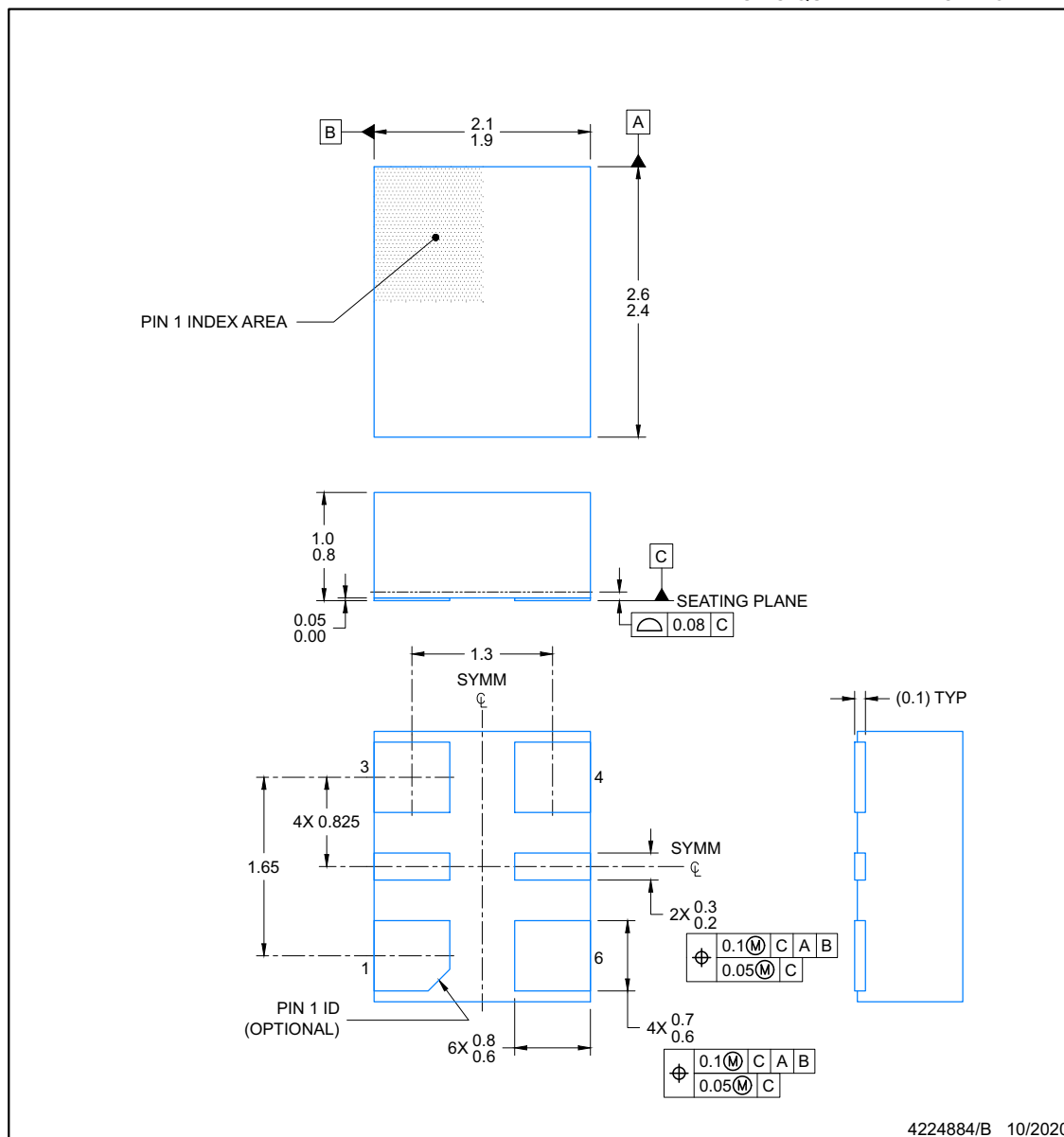
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DLF0006A

PACKAGE OUTLINE

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

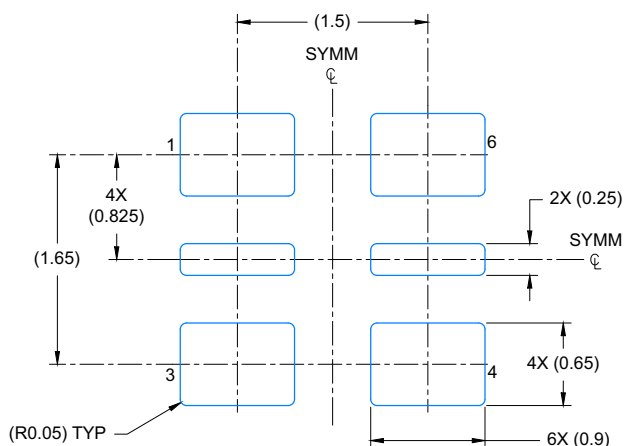
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

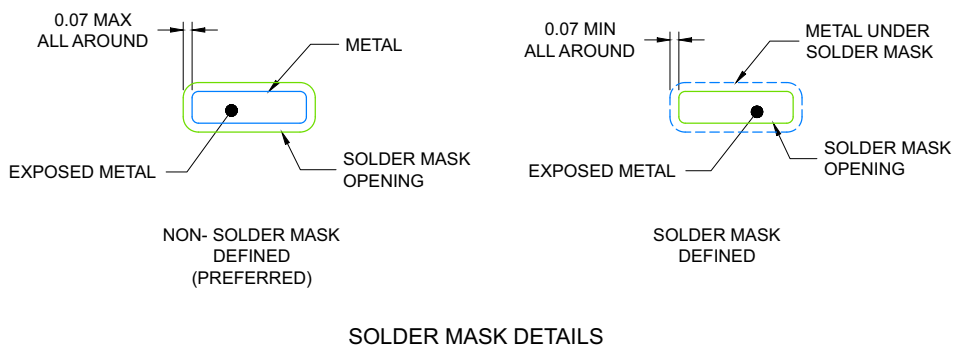
DLF0006A

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



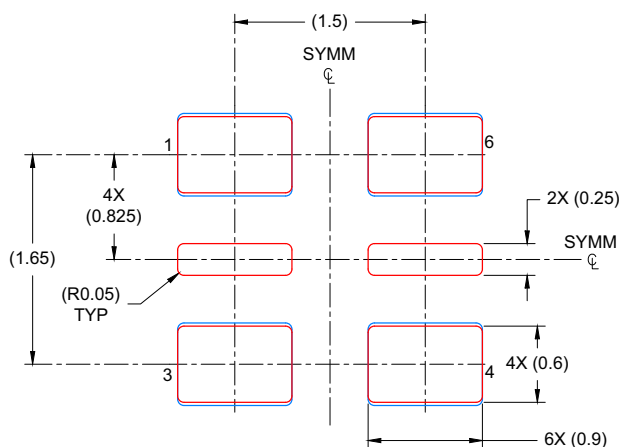
4224884/B 10/2020

NOTES: (continued)

- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271) .

EXAMPLE STENCIL DESIGN**DLF0006A****VSON - 1 mm max height**

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL

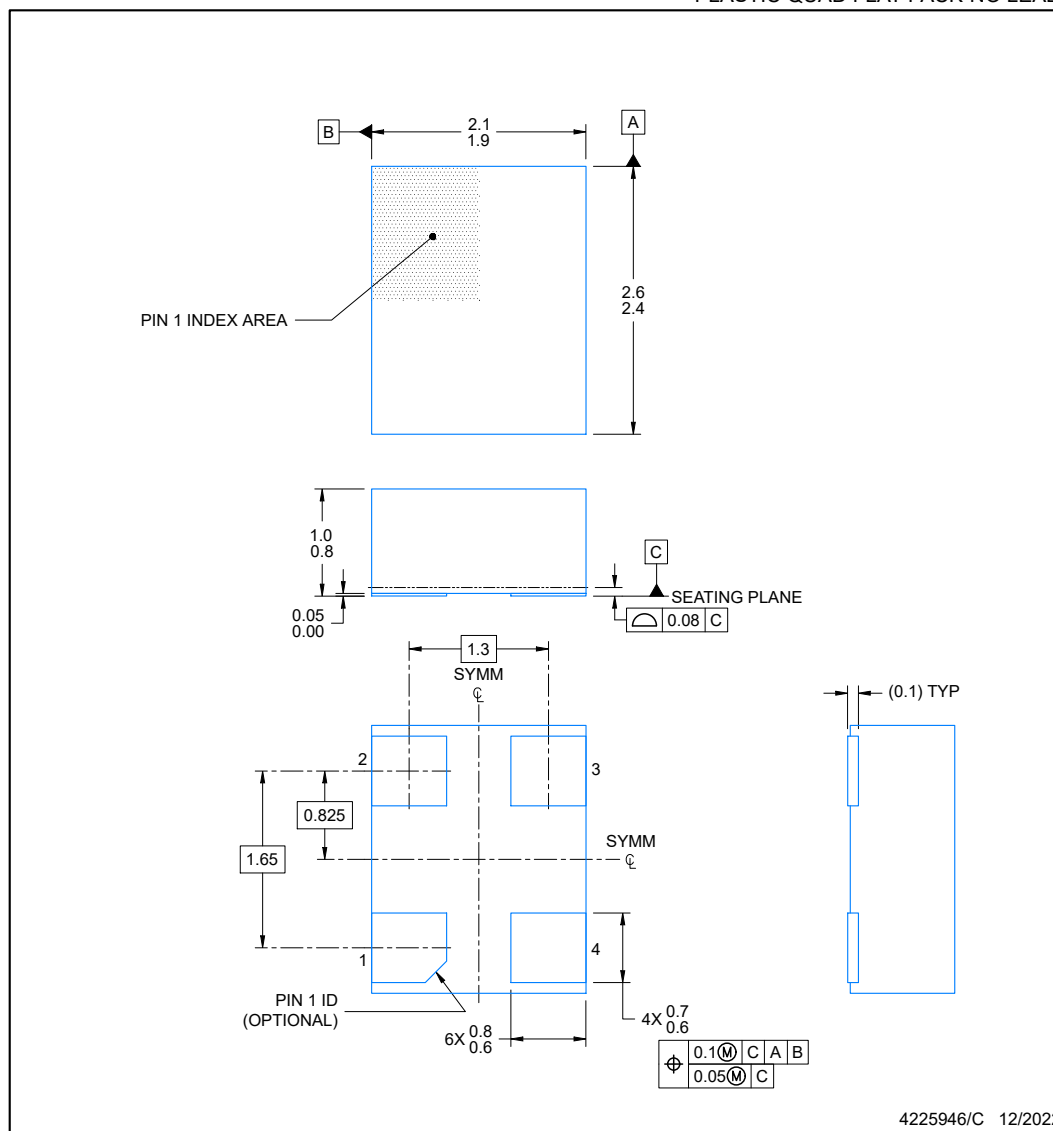
PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
 PADS 1,3,4 & 6: 92%
 SCALE: 20X

4224884/B 10/2020

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE
VSON - 1 mm max height
DLF0004A
PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

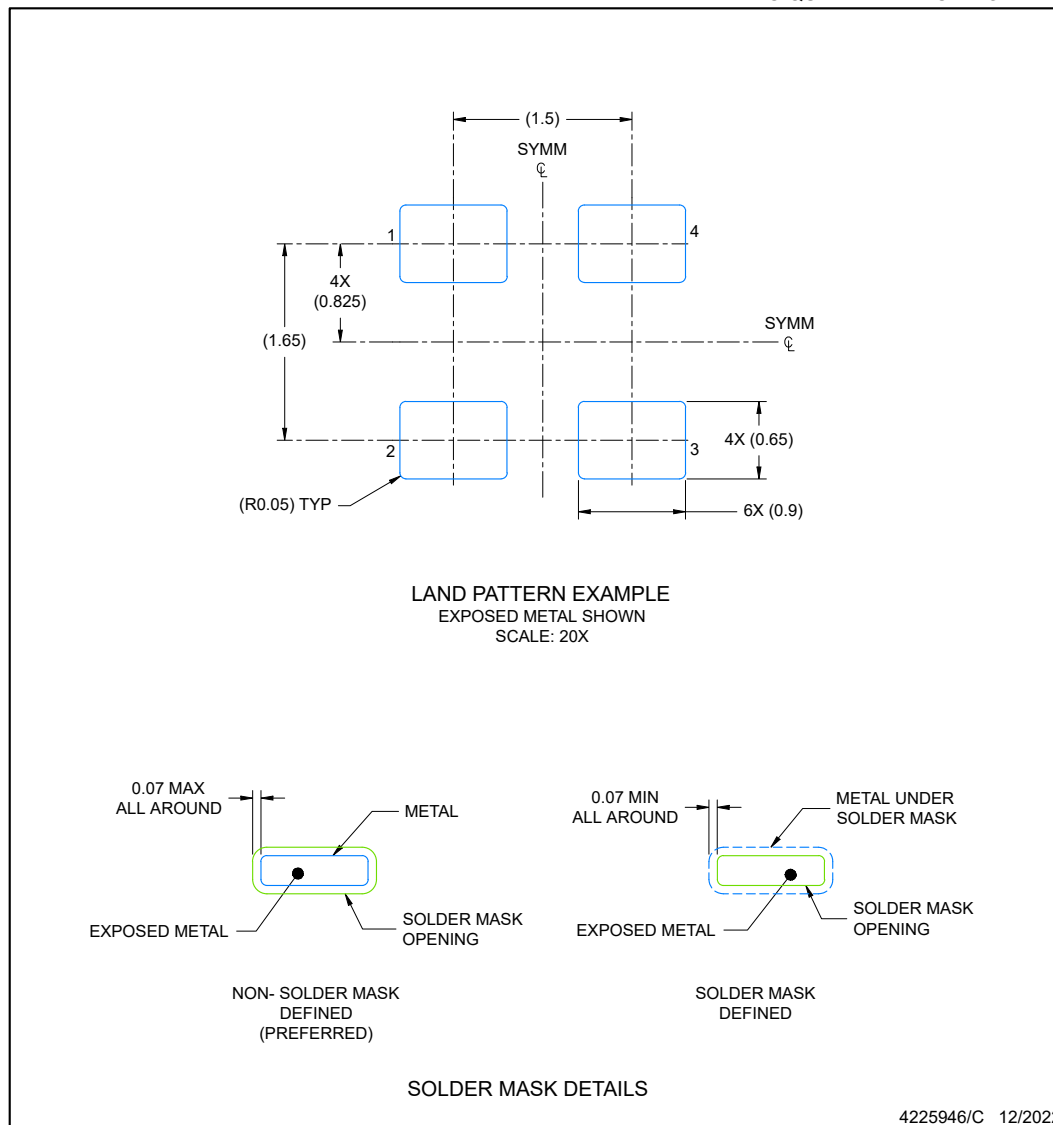
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

DLF0004A

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

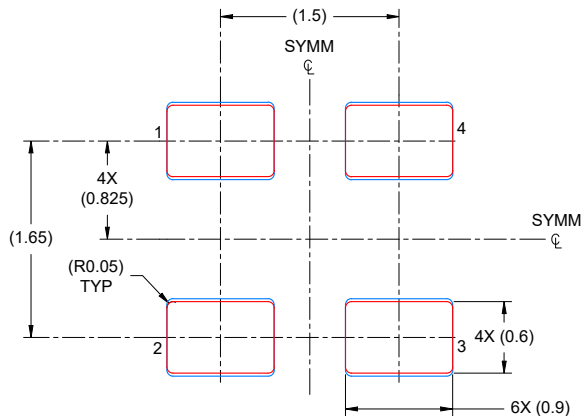
- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).

EXAMPLE STENCIL DESIGN

DLF0004A

VSON - 1 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
PADS 1,3,4 & 6: 92%
SCALE: 20X

4225946/C 12/2022

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK6CE012288CDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCBJ	Samples
LMK6CE012288CDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCBJ	Samples
LMK6CE02500CDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCBG	Samples
LMK6CE02500CDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCBG	Samples
LMK6CE02500DDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC1G	Samples
LMK6CE02500DDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC1G	Samples
LMK6CE03333CDLER	ACTIVE	VSON	DLE	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	HCB8	Samples
LMK6CE03333CDLET	ACTIVE	VSON	DLE	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	HCB8	Samples
LMK6CE04000CDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	HCB6	Samples
LMK6CE04000CDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	HCB6	Samples
LMK6CE04800DDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC1C	Samples
LMK6CE04800DDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC1C	Samples
LMK6CE05000CDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCCB	Samples
LMK6CE05000CDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCCB	Samples
LMK6CE07425DDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC19	Samples
LMK6CE07425DDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC19	Samples
LMK6CE10000CDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCB8	Samples
LMK6CE10000CDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCB8	Samples
LMK6CE10000DDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC18	Samples
LMK6CE10000DDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC18	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK6CE12500CDLER	ACTIVE	VSON	DLE	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCB6	Samples
LMK6CE12500CDLET	ACTIVE	VSON	DLE	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LCB6	Samples
LMK6CE15625DDLFR	ACTIVE	VSON	DLF	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC12	Samples
LMK6CE15625DDLFT	ACTIVE	VSON	DLF	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	LC12	Samples
LMK6DA05184ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDAH	Samples
LMK6DA05184ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDAH	Samples
LMK6DA10000ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA8	Samples
LMK6DA10000ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA8	Samples
LMK6DA12288ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA4	Samples
LMK6DA12288ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA4	Samples
LMK6DA12500ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA6	Samples
LMK6DA12500ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA6	Samples
LMK6DA15552ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA3	Samples
LMK6DA15552ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA3	Samples
LMK6DA15625ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA2	Samples
LMK6DA15625ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA2	Samples
LMK6DA20000ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA1	Samples
LMK6DA20000ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HDA1	Samples
LMK6DA31250ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA0	Samples
LMK6DA31250ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDA0	Samples
LMK6DA40000ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDAM	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK6DA40000ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LDAM	Samples
LMK6HA10000ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA8	Samples
LMK6HA10000ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA8	Samples
LMK6HA10000ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA8	Samples
LMK6HA10000ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA8	Samples
LMK6HA10000BDLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH18	Samples
LMK6HA10000BDLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH18	Samples
LMK6HA15625ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA2	Samples
LMK6HA15625ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LHA2	Samples
LMK6HE40000ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LHGM	Samples
LMK6HE40000ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	Call TI	Level-1-260C-UNLIM	-40 to 85	LHGM	Samples
LMK6PA15625ADLER	ACTIVE	VSON	DLE	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LPA2	Samples
LMK6PA15625ADLET	ACTIVE	VSON	DLE	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LPA2	Samples
LMK6PA15625ADLFR	ACTIVE	VSON	DLF	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LPA2	Samples
LMK6PA15625ADLFT	ACTIVE	VSON	DLF	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LPA2	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of ≤ 1000 ppm threshold. Antimony trioxide based flame retardants must also meet the ≤ 1000 ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

GENERIC PACKAGE VIEW

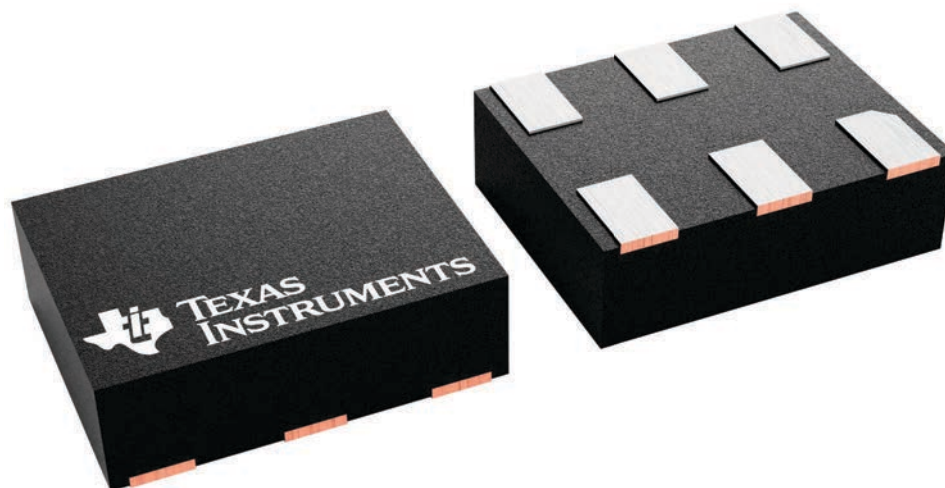
DLE 6

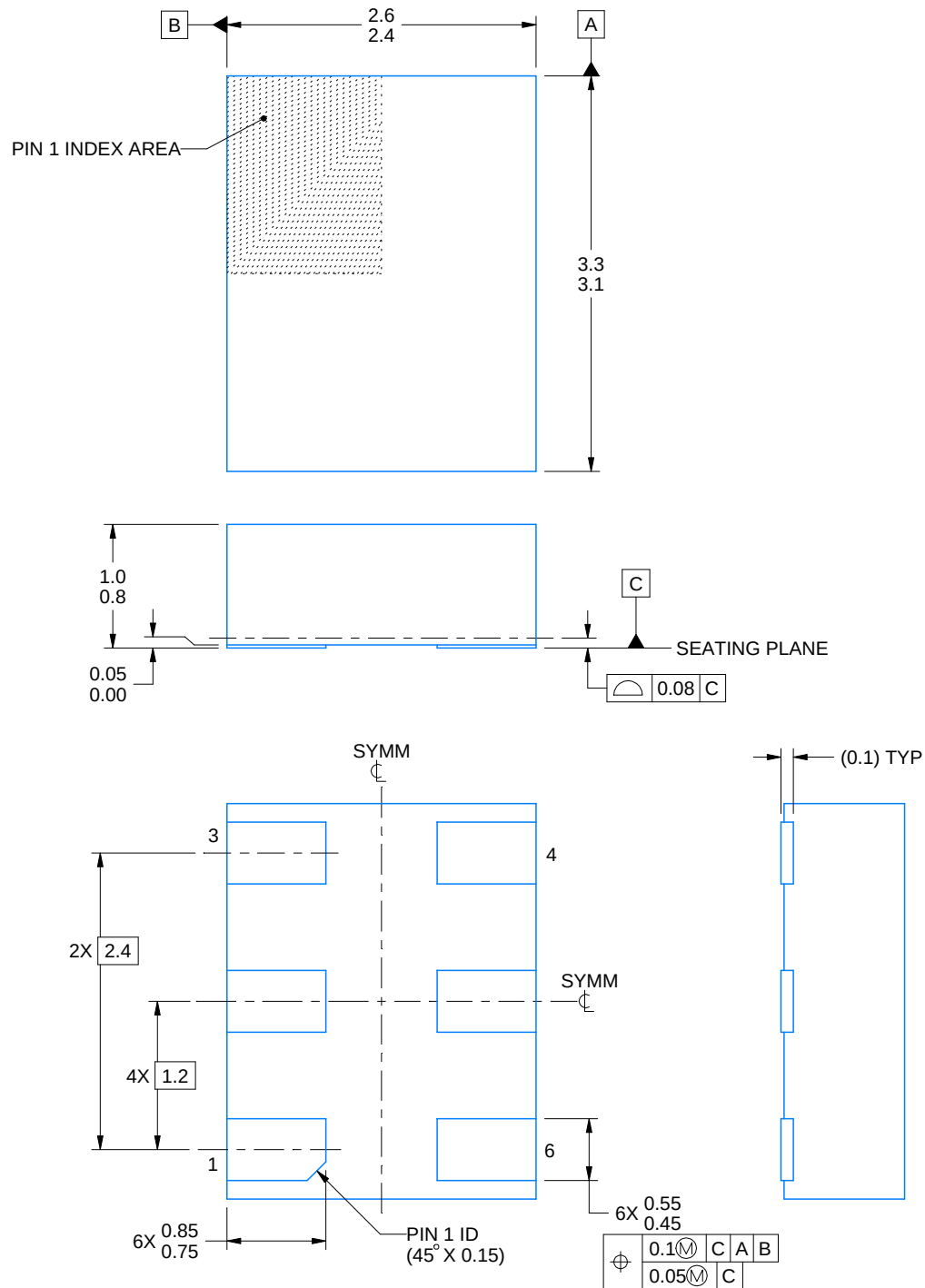
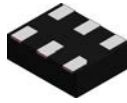
VSON - 1 mm max height

2.5 x 3.2, multiple pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.





4229692/B 12/2023

NOTES:

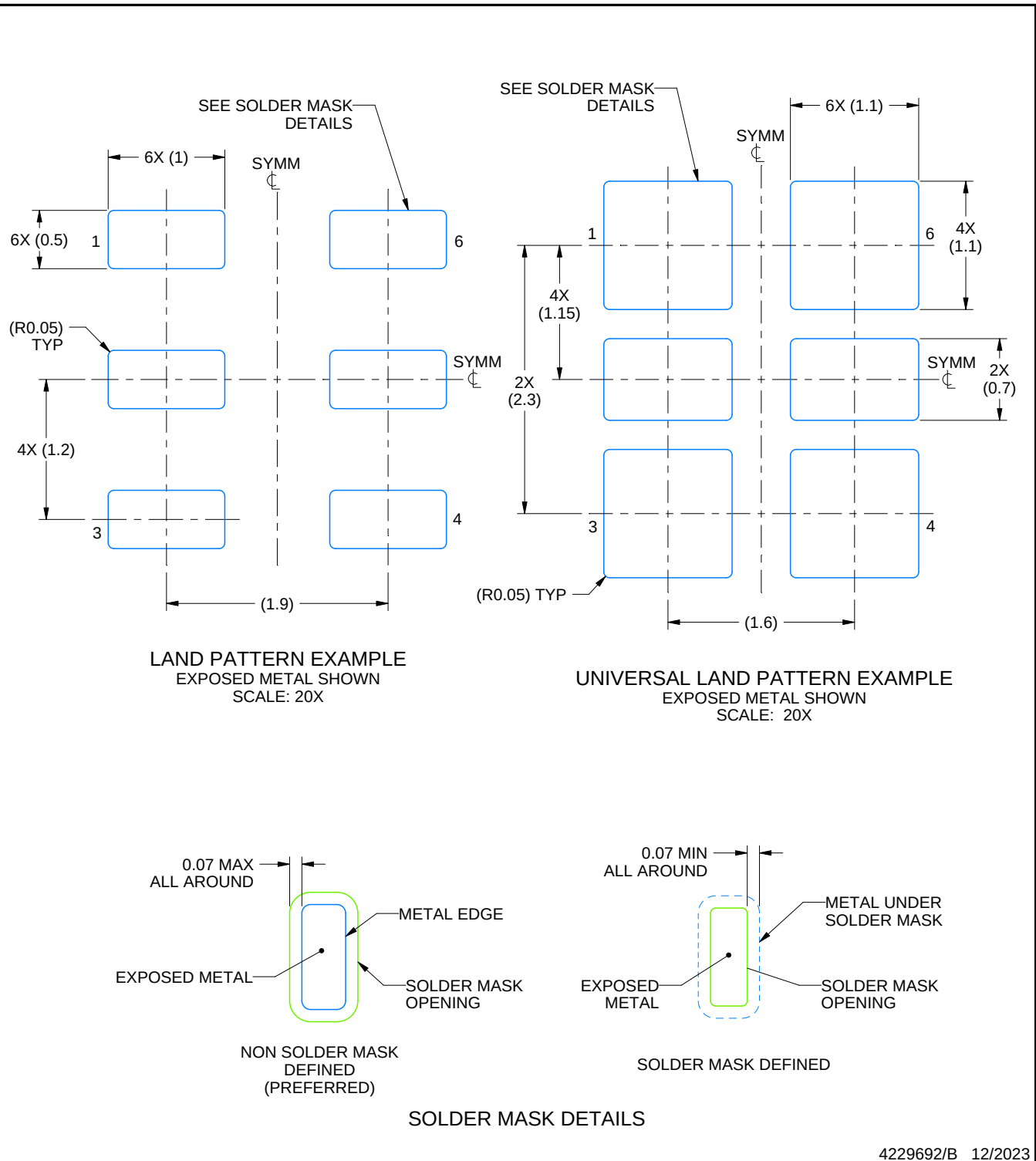
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

DLE0006B

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4229692/B 12/2023

NOTES: (continued)

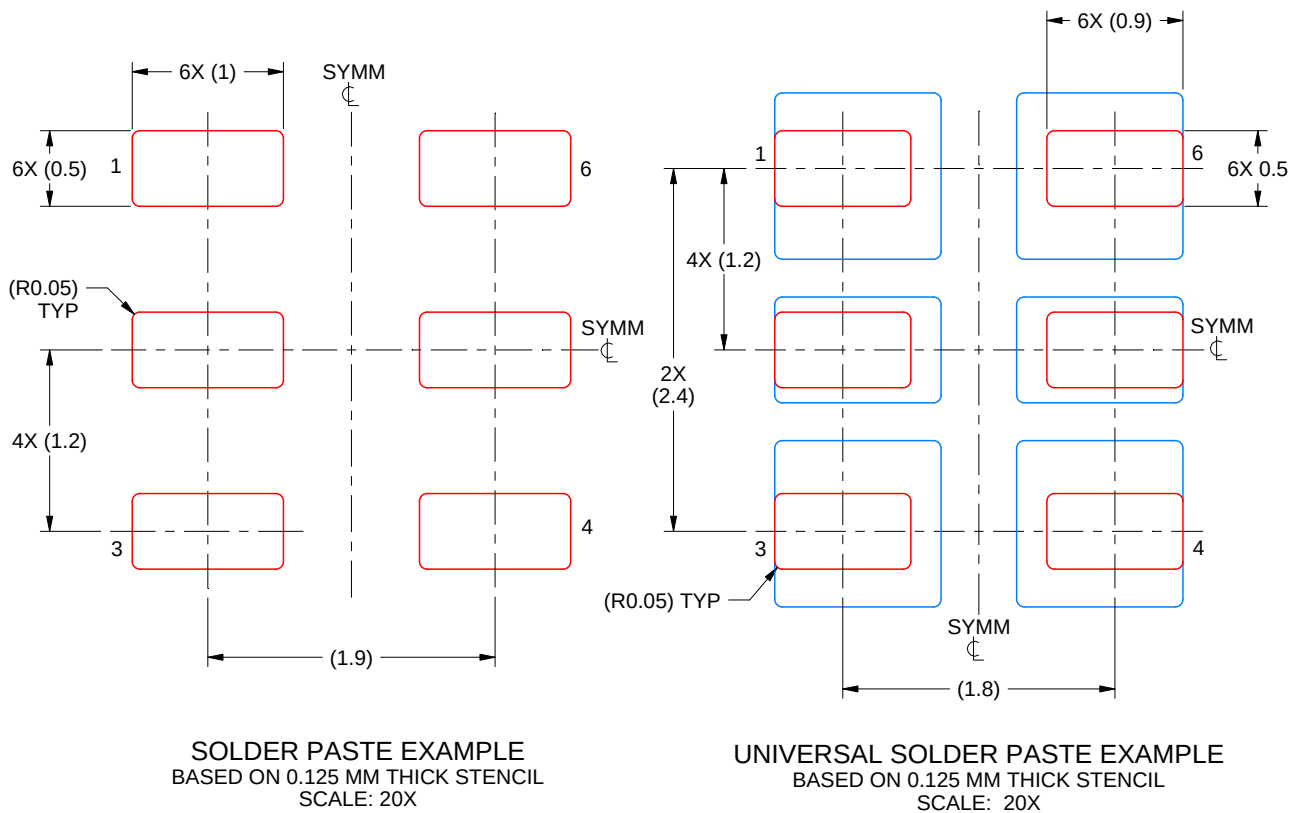
3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

DLE0006B

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



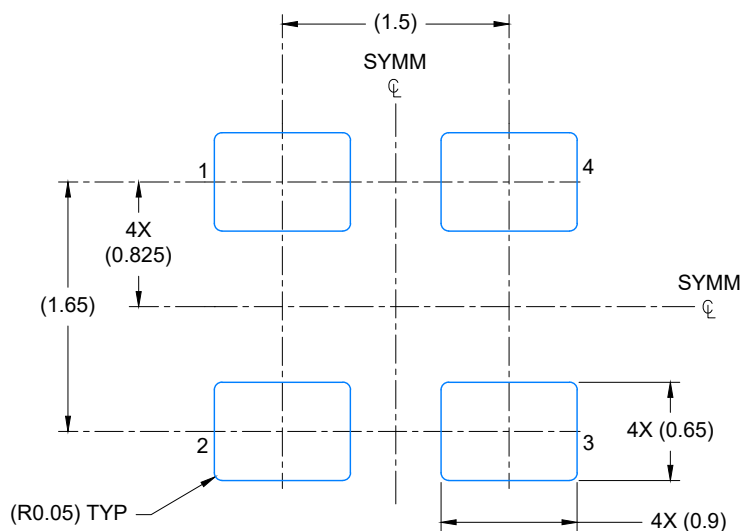
4229692/B 12/2023

NOTES: (continued)

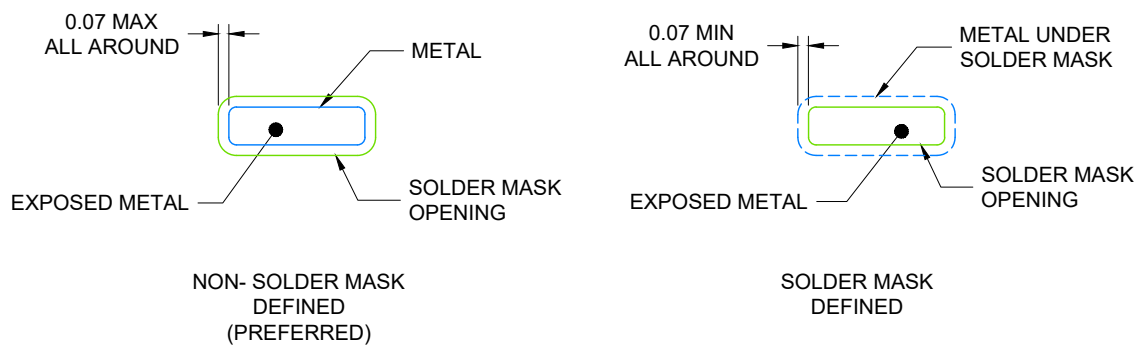
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

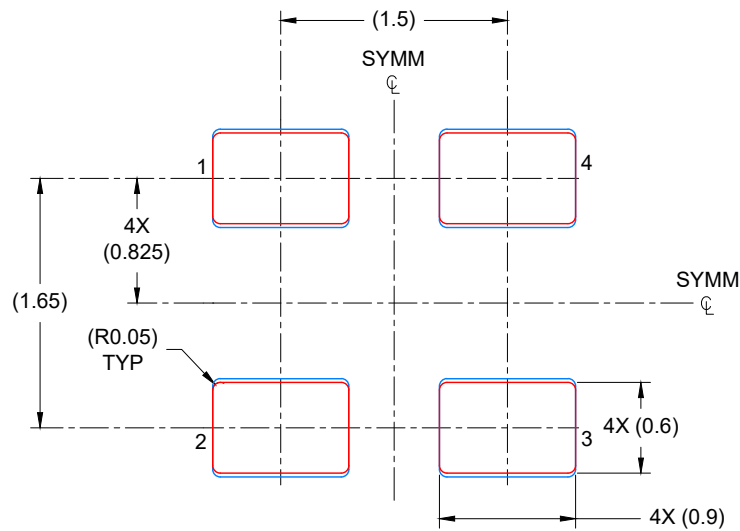


SOLDER MASK DETAILS

4225946/D 03/2023

NOTES: (continued)

- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).



SOLDER PASTE EXAMPLE

BASED ON 0.125 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

PADS 1,3,4 & 6: 92%

SCALE: 20X

4225946/D 03/2023

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

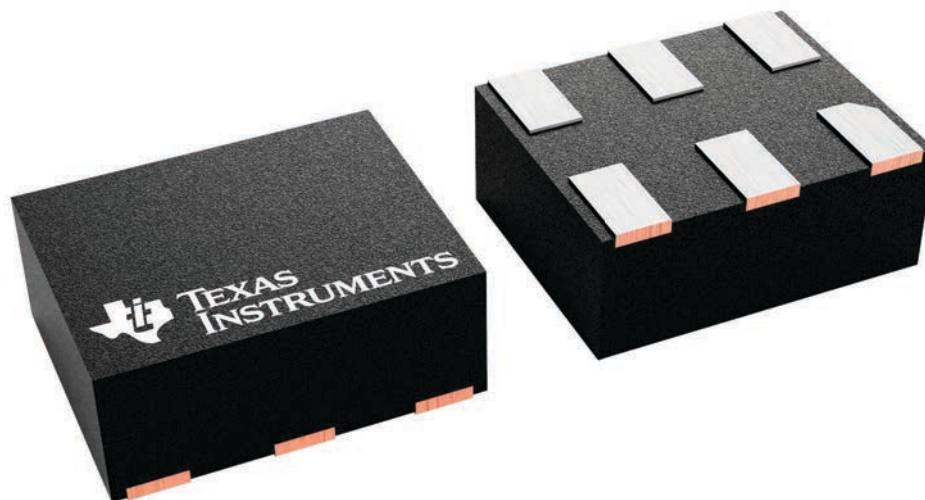
DLF 6

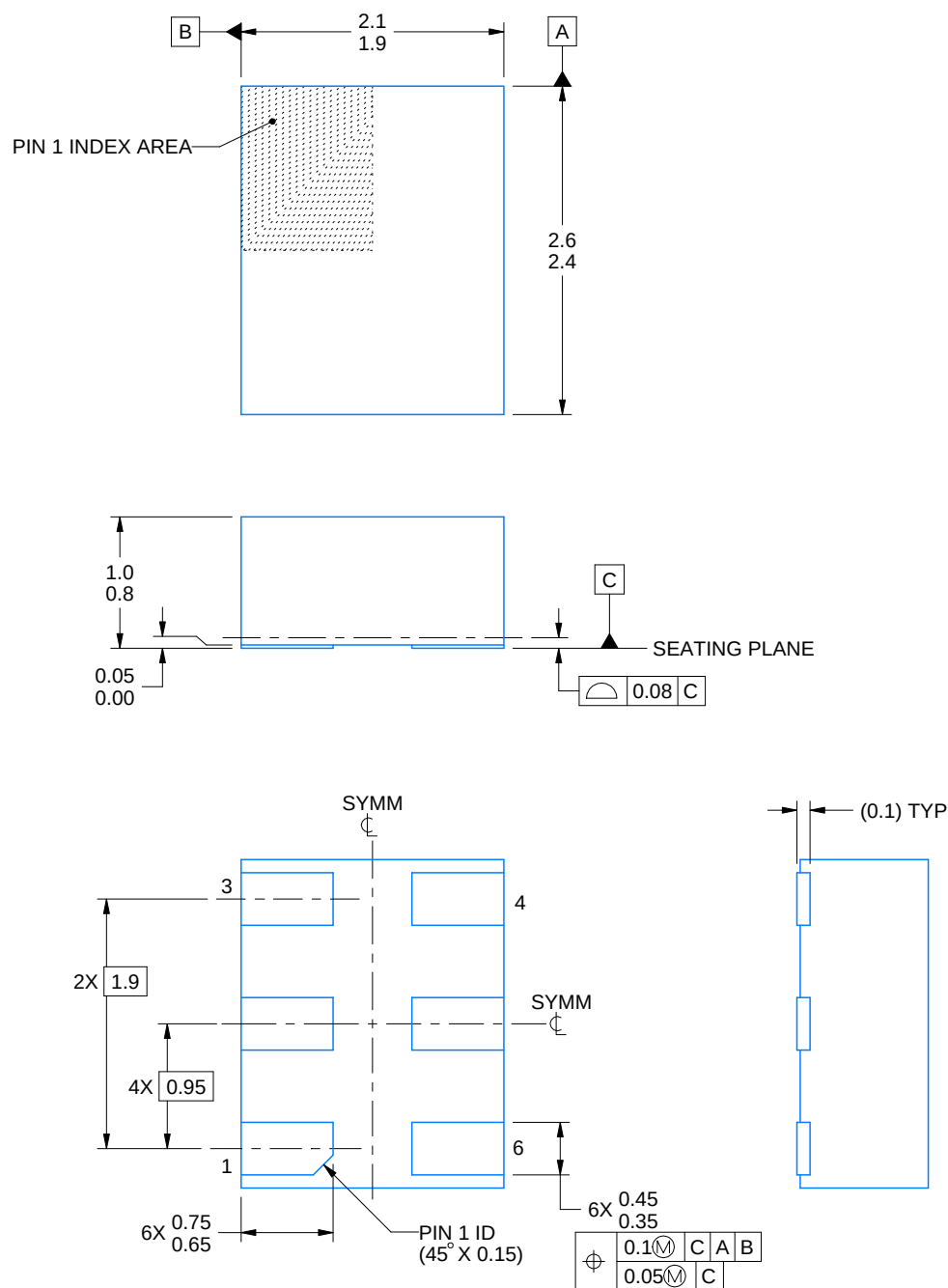
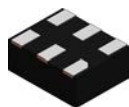
VSON - 1 mm max height

2 x 2.5, multiple pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.





4229693/B 12/2023

NOTES:

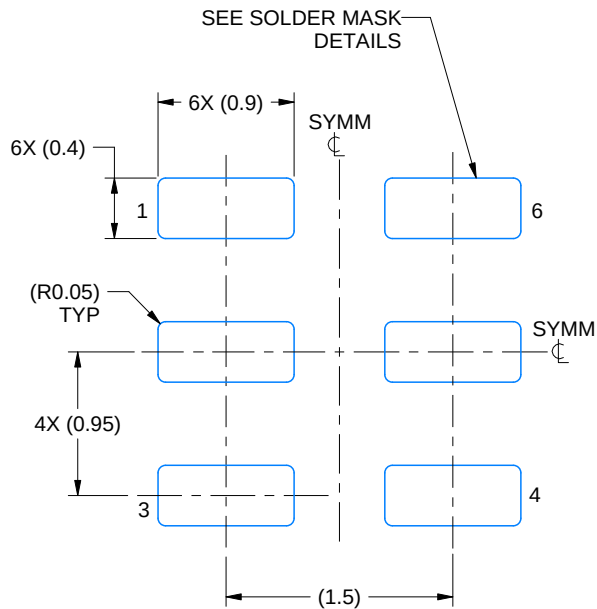
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

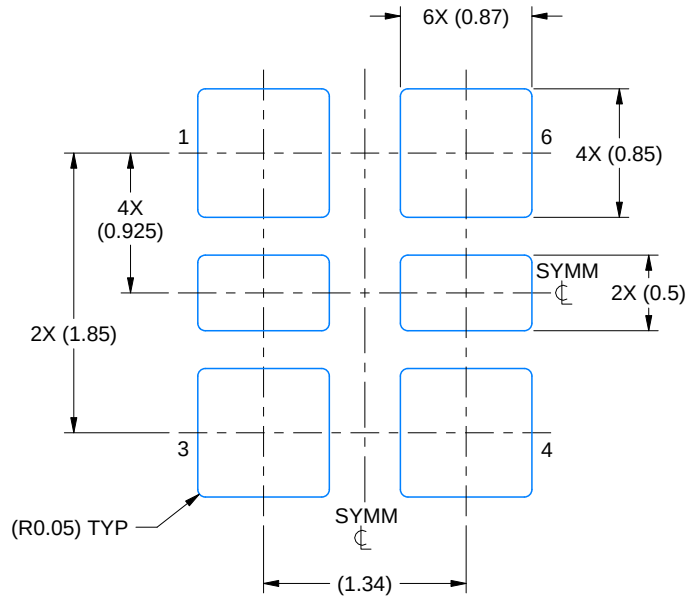
DLF0006B

VSON - 1 mm max height

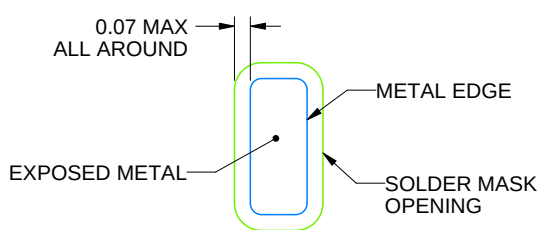
PLASTIC SMALL OUTLINE - NO LEAD



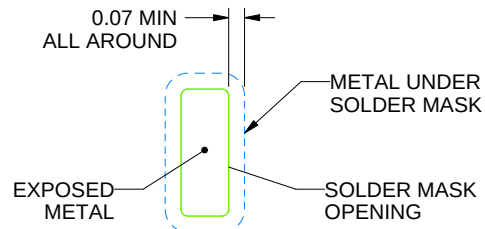
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



UNIVERSAL LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



**NON SOLDER MASK
DEFINED
(PREFERRED)**



SOLDER MASK DEFINED

SOLDER MASK DETAILS

4229693/B 12/2023

NOTES: (continued)

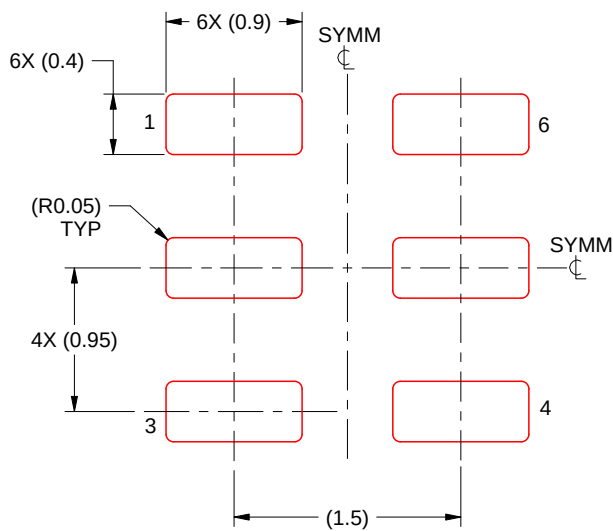
3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).

EXAMPLE STENCIL DESIGN

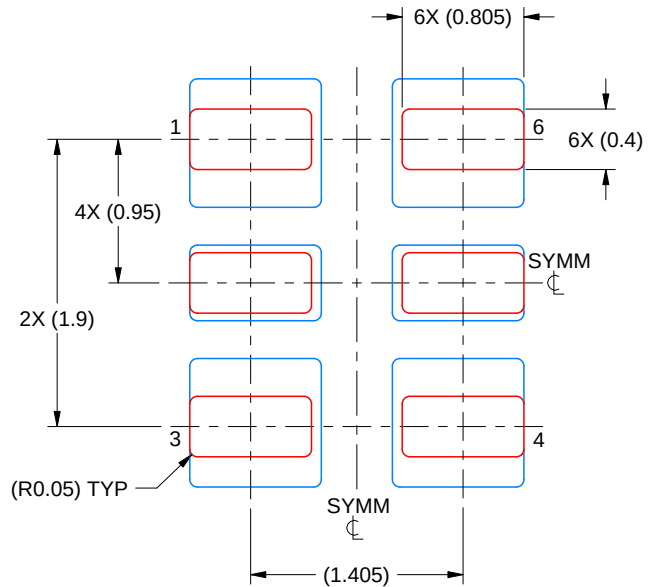
DLF0006B

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE: 20X

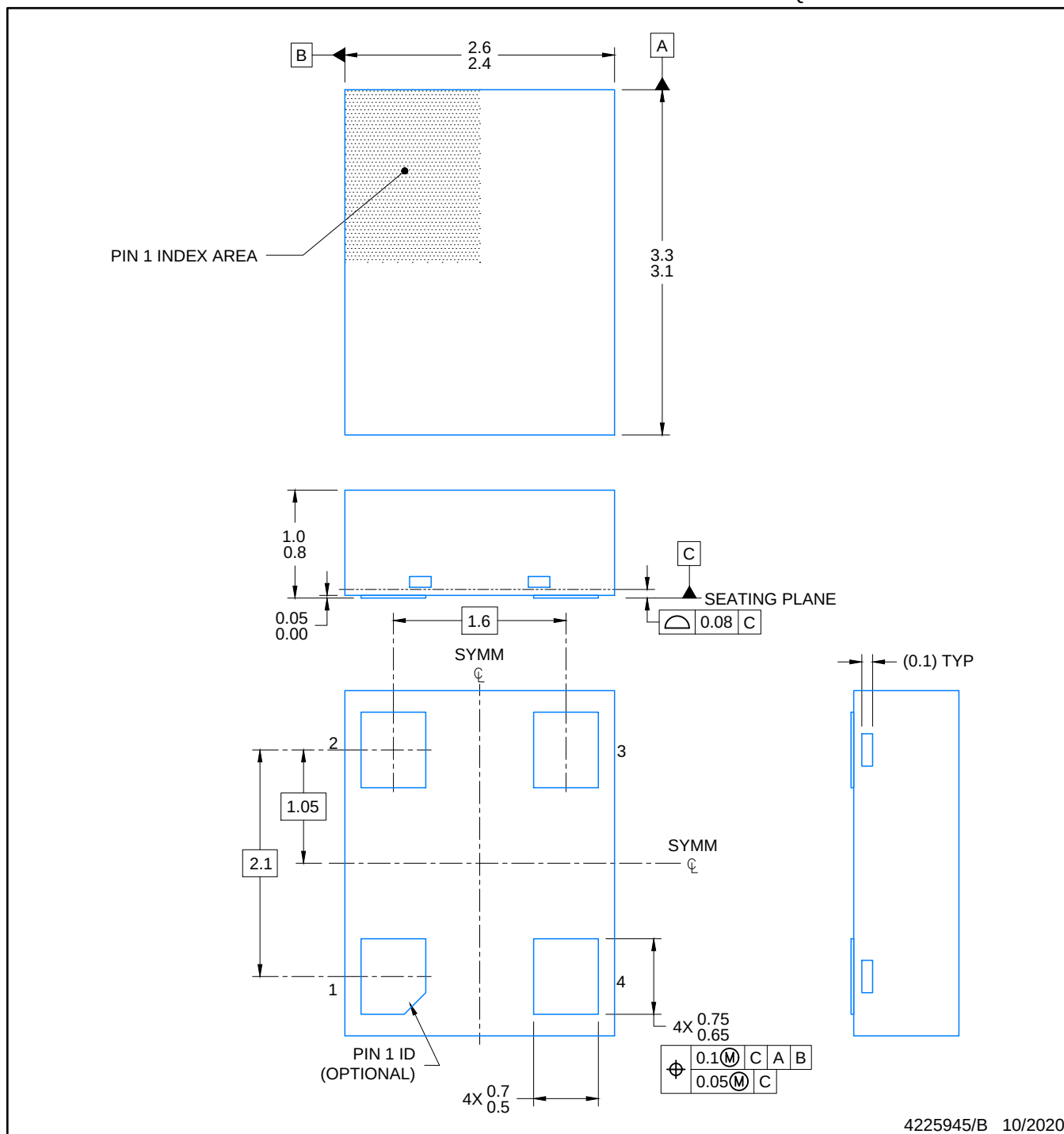


UNIVERSAL SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK
STENCILSCALE 20.000

4229693/B 12/2023

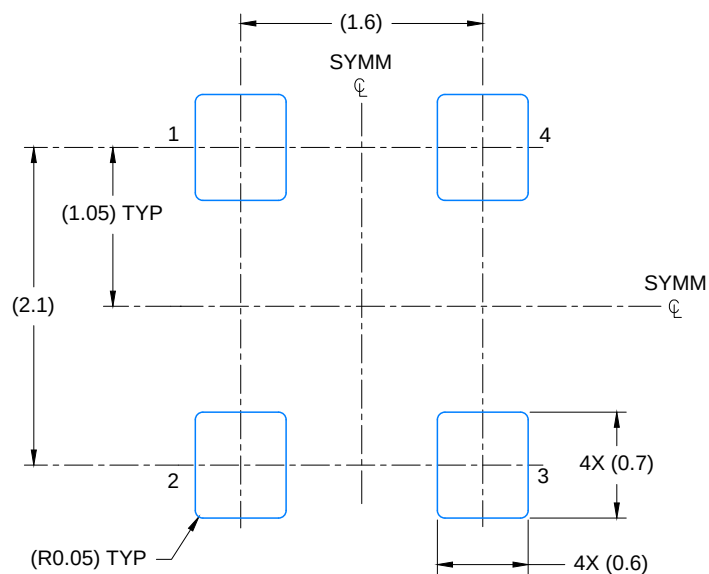
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

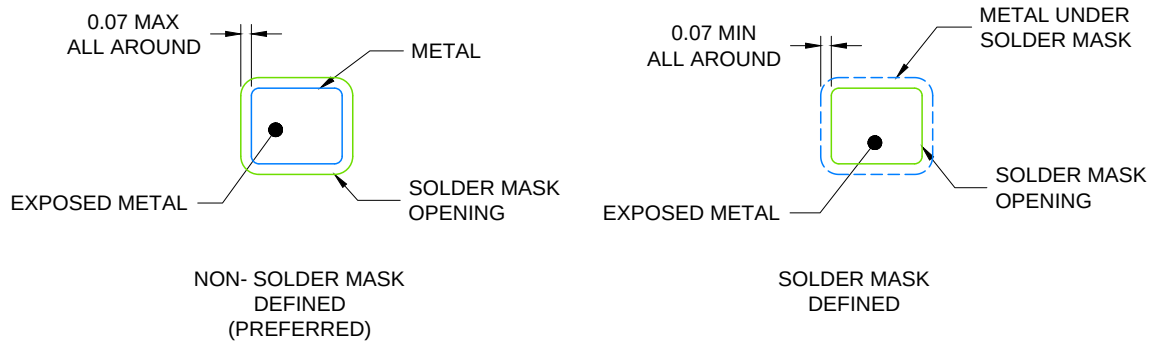


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

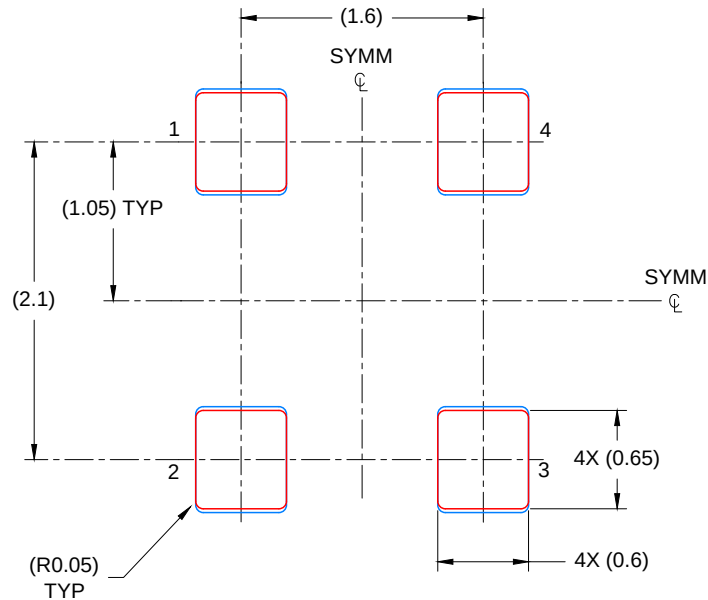


SOLDER MASK DETAILS

4225945/B 10/2020

NOTES: (continued)

- For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271) .



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL
 PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
 ALL PADS: 93%
 SCALE: 20X

4225945/B 10/2020

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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